Spartan-3AN FPGA In-System Flash User Guide

For Spartan®-3AN FPGA applications that read or write data to or from the In-System Flash memory after configuration

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Revision History

The following table shows the revision history for this document.

Date	Version	Revision	
02/26/2007	1.0	Initial release.	
08/29/2007	1.1	Updated throughout. Removed legacy commands not recommended for designs. Added "MultiBoot Configuration Bitstream Guidelines". Simplified discussion in Chapter 7, "Power Management".	
09/24/2007	1.1.1	Added Caution to Chapter 1, "Overview and SPI_ACCESS Interface,", that SPI_ACCESS is not currently supported in simulation.	
04/22/2008	2.0	Updated to reflect current simulation model and timing characteristics.	
01/15/2009	2.1	Added "In-System Flash Change," page 14 to Chapter 1, "Overview and SPI_ACCESS Interface". Updated and clarified default SIM_FACTORY_ID in Table 1-3. Corrected highest byte number in Figure 2-5.	
06/20/2014	2.2	Document updated for in-system flash (ISF) memory transition from wafer fabrication facility X-FAB to UMC as noted in XCN14003.	
10/16/2014	2.3	Revised note 1 and added note 2 in Table 6-9, page 71. Added cautionary note below Table 6-9, page 71. Revised first, second, and third sub-bullet from bottom of page Added a reference to note 1 for the XC3S50AN in Table 6-10, page 72. Added new paragraph and revised the second paragraph under "Extended Device Information Field," page 74.	
06/11/2015	2.4	Added "In-System Flash Change," page 14. Added second sentence to the descriptions for commands 0x9F and 0xD7 in Table 1-5, page 15. Added "Byte 1" to title of Table 6-1, page 65. Added Table 6-2, page 66 and the paragraph preceding it.	

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Overview and SPI_ACCESS Interface

Note: This user guide only applies to Spartan[®]-3AN FPGA designs that access or modify the insystem Flash **after** configuration. This user guide is not required for applications that only use the insystem Flash to configure the FPGA. For Spartan-3AN FPGA configuration information, see UG332: Spartan-3 Generation Configuration User Guide.

Spartan-3AN FPGAs include abundant In-System Flash (ISF) memory. The ISF memory array appears to a Spartan-3AN FPGA application as SPI-based serial Flash memory. The ISF memory is primarily designed to automatically configure the FPGA when power is applied or whenever the PROG_B pin is pulsed Low. However, the ISF memory array is large enough to store...

- two complete, uncompressed FPGA configuration bitstreams. Using the MultiBoot feature, the FPGA application can selectively choose between the two designs or reserve one image as a fail-safe image for live in-system Flash updates.
- additional nonvolatile data for the FPGA application, such as MicroBlaze[™] processor code, serial numbers, Ethernet MAC IDs, graphic images, message templates, and so on.

In-System Flash Summary

Table 1-1, page 8 summarizes the key attributes and capabilities of the ISF memory. The remainder of this user guide describes these features and capabilities in greater detail.

The table also summarizes the amount of Flash memory available to the FPGA application, depending on the number of design options.

- How many FPGA configuration bitstreams are stored in the ISF array?
 - Most applications store a single FPGA configuration bitstream, leaving the remaining space for nonvolatile user data.
 - Optionally, each Spartan-3AN FPGA can store two uncompressed MultiBoot configuration images, which reduces the amount of Flash memory available to the application.
- Does the FPGA application use the ISF memory's Sector Protect or Sector Lockdown features to protect ISF memory contents?
 - Without using the sector-based data protection features, user application data can be stored in the next available page location following the FPGA bitstream (page aligned).
 - If the application uses the sector-based data protection features, then user application data is typically aligned to the next sector boundary (sector aligned).



Table 1-1: In-System Flash Memory Summary

			Spartan-3AN FPGA				
Description		3S50AN	3S200AN	3S400AN	3S700AN	3S1400AN	
In-System Flash (ISF) memory bits	1,081,344 ⁽¹⁾ (1M+)	4,325,376 (4M+)	4,325,376 (4M+)	8,650,752 (8M+)	17,301,504 (16M+)		
SRAM page buffers		1	2	2	2	2	
Default Addressing Mode page size (byte	es)	264	264	264	264	528	
Optional Power-of-2 Addressing Mode pa	ge size (bytes)	256	256	256	256	512	
Pages		512 ⁽¹⁾	2,048	2,048	4,096	4,096	
Blocks		64 ⁽¹⁾	256	256	512	512	
Sectors		4(1)	8	8	16	16	
Pages per Block		8	8	8	8	8	
Pages per Sector		128	256	256	256	256	
Bytes per Block		2,112	2,112	2,112	2,112	4,224	
Bytes per Sector		33,792	67,584	67,584	67,584	135,168	
FPGA configuration bitstream size (uncon	mpressed)	437,312	1,196,128	1,886,560	2,732,640	4,755,296	
Pages required for FPGA bitstream,	Default	208	567	894	1,294	1,126	
always starting at page 0	Power-of-2	214	585	922	1,335	1,161	
Page Aligned User Data (maximizes ava	ailable data sp	ace but limits	Sector Pro	otect, Secto	r Lockdow	n features)	
Pages available for user application beyond FPGA configuration bitstream, data aligned to next page boundary, Default Addressing Mode		304 ⁽¹⁾	1,481	1,154	2,802	2,970	
Total Flash memory bits available for use Default Addressing Mode	642,048 ⁽¹⁾ (627K) (0.61M)	3,127,872 (3,054K) (2.98M)	2,437,248 (2,380K) (2.32M)	5,917,824 (5,779K) (5.64M)	12,545,280 (12,251K) (11.96M)		
Sector Aligned User Data (user data ali	gned to sector	s for Sector	Protect, Se	ctor Lockdo	wn feature	s)	
Sectors required per uncompressed FPGA	bitstream	2	3	4	6	5	
Sectors available for user application beyonfiguration bitstream, aligned to next suboundary	2(1)	5	4	10	11		
Total bits available for user application in sectors, Default Addressing Mode	540,672 ⁽¹⁾ (528K) (0.51M)	2,703,360 (2,640K) (2.57M)	2,162,688 (2,112K) (2.06M)	5,406,720 (5,280K) (5.15M)	11,894,784 (11,616K) (11.34M)		
MultiBoot FPGA Configuration		+	-	+	-		
Maximum number of uncompressed Mul configuration images	2 ⁽¹⁾	2	2	2	2		
Total sectors available for user application MultiBoot FPGA configuration bitstreams	0(1)	2	0	4	6		
Total Flash memory bits available for user beyond MultiBoot FPGA configuration bits sector aligned, Default Addressing Mode	0(1)	1,081,344 (1,056K) (1.03M)	0	2,162,688 (2,112K) (2.06M)	6,488,064 (6,336K) (6.18M)		

Notes:

 $1. \ \ Maximum \ supported \ by \ the \ Xilinx \ tools. \ See \ "In-System \ Flash \ Change," \ page \ 14.$



Accessing In-System Flash Memory After Configuration

SPI_ACCESS Design Primitive

After the FPGA configures, the application loaded into the FPGA can access the ISF memory using a special design primitive called SPI_ACCESS, shown in Figure 1-1. All data accesses to and from the ISF memory are performed using an SPI serial protocol. Neither the Spartan-3AN FPGA itself nor the SPI_ACCESS primitive includes a dedicated SPI master controller. Instead, the control logic is implemented using the FPGA's programmable logic resources. The SPI_ACCESS primitive essentially connects the FPGA application to the In-System Flash memory array.

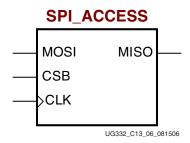


Figure 1-1: SPI_ACCESS Primitive (only available on Spartan-3AN FPGAs)

Table 1-2 describes the connections to the SPI_ACCESS primitive. The serial data lines are names relating to the logic that drives the data. The FPGA application is always the Master of each SPI transaction; the ISF memory is always the Slave.

Table 1-2:	SPI_ACCESS Primitive Connections
------------	----------------------------------

Port Name	Direction	Function		
MISO Output		Master Input, Slave Output. Serial data output from the ISF memory array back to the FPGA logic.		
MOSI Input		Master Output, Slave Input. Serial data input to the ISF memory array from the FPGA logic.		
CSB Input		Active-Low chip-enable to ISF memory array, driven by FPGA logic.		
CLK Input		Clock input to ISF memory array, driven by FPGA logic.		

Table 1-3 describes the available attributes for the SPI_ACCESS primitive.

Table 1-3: SPI_ACCESS Primitive Attributes

Attribute	Туре	Allowed Values	Default	Description
SIM_DEVICE	String	"3S50AN", "3S200AN", "3S400AN", "3S700AN" or "3S1400AN"	"UNSPECIFIED"	Specifies the target device so that the proper size SPI Memory is used. This attributes required to be set.
SIM_USER_ID	64-byte Hex Value	Any 64-byte hex value	All locations default to 0xFF	Specifies the programmed USER ID in the Security Register for the SPI Memory



Table 1-3: SPI_ACCESS Primitive Attributes (Continued)

Attribute	Туре	Allowed Values	Default	Description
SIM_MEM_FILE	String	Specified file and directory name	"NONE"	Optionally specifies a hex file containing the initialization memory content for the SPI Memory.
SIM_FACTORY_ID	64-byte Hex Value	Any 64-byte Hex Value	All locations default to 0x00	Specifies the unique identifier value in the Security Register for simulation purposes (the actual hardware value will be specific to the particular device used). See "Security Register" in Chapter 9.
SIM_DELAY_TYPE	String	"ACCURATE", "SCALED"	"SCALED"	Scales down some timing delays for faster simulation run. "ACCURATE" = timing and delays consistent with datasheet specs. "SCALED" = timing numbers scaled back to run faster simulation, behavior not affected.

HDL Instantiation Examples

The SPI_ACCESS design primitive must be instantiated in an HDL design; it cannot be inferred by the logic synthesis software.

Caution! Only a subset of the commands available in hardware are supported in simulation for the SPI_ACCESS primitive. Please see the Simulation Support section for a list of these commands.

VHDL

The SPI_ACCESS primitive requires that the Xilinx Unisim Library be declared. Instantiate the SPI_ACCESS component and connect it to the other signals in the design.

Xilinx Unisim Library

The Xilinx Unisim library includes definitions for all the Spartan-3AN FPGA design primitives, including the SPI_ACCESS primitive. Declare the Unisim library before the **entity** declaration.

```
library UNISIM;
use UNISIM.VComponents.all;
entity XXXX is
```

Instantiate SPI_ACCESS Primitive

Instantiate the SPI_ACCESS design primitive after the **architecture** declaration. Connect each of the four SPI_ACCESS ports to a signal name in the FPGA application.

```
architecture Behavioral of XXXX is
begin
...
SPI_ACCESS_inst: SPI_ACCESS
generic map (
    SIM_DEVICE => "3S700AN"
)
port map (
    MISO => MISO_signal, -- 1-bit SPI output data
    MOSI => MOSI_signal, -- 1-bit SPI input data
```



```
CSB => CSB_signal, -- 1-bit SPI chip enable
CLK => CLK_signal -- 1-bit SPI clock input
);
-- End of SPI ACCESS inst instantiation
```

Verilog

Using Verilog, simply connect the SPI_ACCESS design primitive to signal names within the FPGA application.

```
SPI_ACCESS #(
.SIM_DEVICE("3S700AN")
) SPI_ACCESS_inst (
   .MISO(MISO_signal), // 1-bit SPI output data
   .MOSI(MOSI_signal), // 1-bit SPI input data
   .CSB(CSB_signal), // 1-bit SPI chip enable
   .CLK(CLK_signal) // 1-bit SPI clock input
);
// End of SPI ACCESS inst instantiation
```

SPI Transactions

The SPI_ACCESS primitive uses a typical SPI serial transaction protocol. By default, the interface supports SPI "Mode 3" transfers.

Caution! Only a subset of the commands available in hardware are supported in simulation for the SPI_ACCESS primitive. Please see the Simulation Support section for a list of these commands.

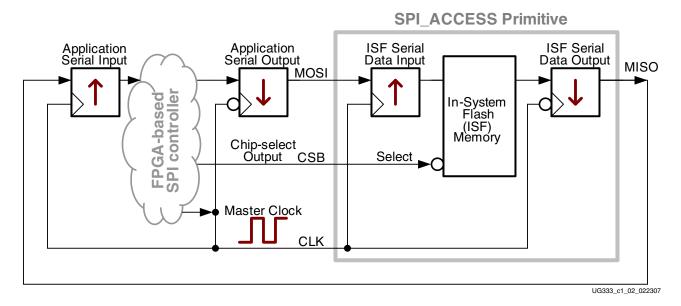


Figure 1-2: FPGA-to-SPI_ACCESS Interface and Active Clock Edges

- All transactions are controlled by a SPI Master controller, built using FPGA logic.
- All transactions are synchronized by the CLK input on the SPI_ACCESS primitive. The FPGA application generates the CLK signal.
- The SPI protocol uses both the rising and falling edges of the CLK signal.



- The FPGA application selects the ISF memory by driving the SPI_ACCESS CSB input Low when the CLK input is High and de-selects the ISF memory by driving the CSB input High.
- When CSB returns High, the current command is terminated.
- The SPI Master, which is the FPGA application, starts every transaction by supplying a command code or command sequence to the SPI_ACCESS MOSI input.
- The CSB select input must be Low throughout the duration of a transaction. It cannot change during the middle of an operation. Some ISF memory operations, such as erasing a page or sector, continue automatically even after the SPI transaction is complete.
- The FPGA application supplies data to the ISF memory via the SPI_ACCESS MOSI input, clocked on the falling edge of CLK.
- The ISF memory captures any data supplied on the SPI_ACCESS MOSI input using the rising edge of CLK.
- The ISF memory presents data or status on the SPI_ACCESS MISO output using the falling edge of CLK.
- The FPGA application captures any data supplied by the ISF memory on the SPI_ACCESS MISO output using the rising edge of CLK.
 - Because MISO output data changes every falling edge of CLK, the FPGA can also capture data on the falling edge of CLK to simplify the FPGA application.
- All data, commands, and address information are supplied serially, ordered from most-significant bit to least-significant bit.
- When the CSB select input is High to deselect the ISF memory, the SPI_ACCESS MISO output is High.

Example Detailed Command Sequence

Figure 1-3 provides a detailed example of a command sequence that reads the Status Register. This example shows the relation of the various control signals and the clock edges when data appears and is captured.

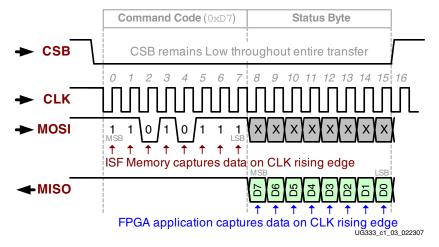


Figure 1-3: Status Register Read Command Sequence



- 1. The FPGA application starts the command by driving the SPI_ACCESS CSB input Low, while the CLK input is High. Subsequently, the CSB input must remain Low throughout the entire transfer.
- 2. The Status Register Read command code is 0xD7, as detailed in Table 6-8, page 69. As mentioned in "SPI Transactions," all data is transferred most-significant bit first. Consequently, the FPGA application clocks in the binary pattern "11010111" on the MOSI input, synchronized to the falling edge of CLK.
- The ISF memory captures the command sequence on the rising edge of CLK, as indicated.
- 4. Before data appears, the MISO output is High.
- 5. After all eight command bits are transferred, the ISF memory provides the current Status Register contents on the SPI_ACCESS MISO output. Again, the data appears most-significant bit first, synchronized to the falling edge of CLK.
- 6. The FPGA application captures the ISF status information on the rising edge of CLK.
- 7. After receiving the last bit of status information, the FPGA application drives the CSB input High to end the transaction.

Simulation Support

The SPI_ACCESS simulation model supports only a subset of the total commands that can be run in hardware. The commands that are supported in the model are shown below in Table 1-4. These have been tested and verified to work in the model and on silicon. All other commands are not supported in the simulation model, though they will work as expected in hardware. For more information on the SPI_ACCESS primitive and simulation model, please refer to the ISE® software Synthesis and Simulation Design Guide or the Spartan-3A and Spartan-3A DSP Libraries Guide for HDL Designs.

Table 1-4: SPI_ACCESS Simulation Supported Commands

Command	Common Application	Hex Command Code
Fast Read	Reading a large block of contiguous data, if CLK frequency is above 33 MHz	0x0B
Random Read	Reading bytes from randomly-addressed locations, all read operations at 33 MHz or less	0x03
Status Register Read	Check ready/busy for programming commands, result of compare, protection, addressing mode, etc.	0xD7
Information Read	Read JEDEC Manufacturer and Device ID	0x9F
Security Register Read	Performs a read on the contents of the security register.	0x77
Security Register Program	Programs the User-Defined Field in the Security Register	0x9B
Buffer Write	Write data to SRAM page buffer; when complete, transfer to ISF memory using Buffer to Page Program command	Buffer1- 0x84 Buffer2- 0x87
Buffer to Page Program with Built- in Erase	First erases selected memory page and programs page with data from designated buffer	Buffer1- 0x83 Buffer2- 0x86



Table 1-4: SPI_ACCESS Simulation Supported Commands (Continued)

Command	Common Application	Hex Command Code
Buffer to Page Program without Built-in Erase	Program a previously erased page with data from designated buffer	Buffer1- 0x88 Buffer2- 0x89
Page Program Through Buffer with Erase	Combines Buffer Write with Buffer to Page Program with Built-in Erase command	Buffer1- 0x82 Buffer2- 0x85
Page to Buffer Compare	Verify that the ISF memory array was programmed correctly	Buffer1- 0x60 Buffer2- 0x61
Page to Buffer Transfer	Transfers the entire contents of a selected ISF memory page to the specified SRAM page buffer	Buffer1- 0x53 Buffer2- 0x55
Sector Erase	Erases any unprotected, unlocked sector in the main memory	0x7C
Page Erase	Erases any individual page in the ISF memory array	0x81

In-System Flash Change

As noted in $\underline{XCN14003}$, the in-system flash (ISF) memory for the Spartan-3AN FPGA devices is transitioning from wafer fabrication facility X-FAB (0.13 µm process) to UMC (0.11 µm process). There are differences between the X-FAB ISF and the UMC ISF that might impact programming or usage, as described in Xilinx Answer 59572.

- The XC3S50AN-TQ(G)144 ISF changes from a 1 Mb density from X-FAB to a 2 Mb density from UMC. See "XC3S50AN In-System Flash Change".
- The number of optional extended device information (EDI) bytes is different between the X-FAB ISF and UMC ISF. The X-FAB ISF has no additional EDI bytes and the UMC ISF has one additional byte. The Information Read command extended info is different. For only the X-FAB ISF, the extended info byte 5 value is 0x00. For only the UMC ISF, the extended info byte 5 value is 0x01. See Table 6-9, page 71, Table 6-14, page 74, and Table 6-15, page 74 for details.
- The ISF Status register changes from a 1-byte register from X-FAB to a 2-byte register from UMC (see "Status Register," page 65).
- XC3S700AN T_{PEP} Max is 55 ms for devices with the ISF from UMC (see Table 4-4, page 45).
- XC3S700AN T_{PE} Max is 50 ms for devices with the ISF from UMC (see Table 5-4, page 56).

XC3S50AN In-System Flash Change

As noted in $\underline{XCN14003}$, the in-system flash (ISF) memory for the Spartan-3AN FPGA devices is transitioning from wafer fabrication facility X-FAB (0.13 µm process) to UMC (0.11 µm process). The XC3S50AN-TQ(G)144 ISF changes from a 1 Mb density (1,081,344 bits) to a 2 Mb density (2,162,688 bits). The XC3S50AN-FT(G)256 is not affected by $\underline{XCN14003}$ because it has been discontinued by PDN $\underline{XCN13016}$.

Xilinx tools and programming solutions support programming and data file generation for only the first 1 Mb of the 2 Mb UMC ISF, to keep compatibility with both updated and original devices. The new UMC ISF supports the same commands and has the same page



sizes as the original X-FAB ISF. Thus, the UMC ISF is compatible with the operations and functions of the X-FAB ISF for the first 1 Mb of its memory array.

The UMC ISF has a few differences shown in Table 1-5 that can require updates to programming solutions or FPGA designs. As a result, ancillary programming algorithm changes are required for the XC3S50AN-TQ(G)144 and are specified in the Xilinx Answer 59572.

Table 1-5: In-System Flash Changes for the XC3S50AN-TQ(G)144 with XCN14003

In-System Flash Command	X-FAB In-System Flash Attribute	UMC In-System Flash Attribute	Description
N/A	Density = 1 Mb	Density = 2 Mb	The in-system flash density is different.
0x9F (Information Read)	Second byte = 00100010b	Second byte = 00100011b	The in-system flash Device ID/density code (second byte of the 3-byte value from the Information Read command) is different. Also note that the extended information is different, as described in "In-System Flash Change".
0xD7 (Status Register Read)	First byte, bits[5:2] = 0011b	First byte, bits[5:2] = 0101b	The in-system flash Status register density code bits[5:2] are different. Also note that the Status Register is 2 bytes in the UMC ISF, as described in "In-System Flash Change".

Wrapping Considerations

As described in Chapter 3, "Read Commands", after reading the last bit in the memory, the ISF continues reading but returns to the beginning of the first page of memory, with no added delay. For the XC3S50AN with the larger 2 Mb UMC ISF, the ISF needs to read through the second 1 Mb of data before wrapping back to the beginning of the first page.

Related Materials and References

UG332: Spartan-3 Generation Configuration User Guide

• Includes specific information on configuration from the internal SPI Flash in Chapter 10, and general information on configuration including MultiBoot.

UG331: Spartan-3 Generation FPGA User Guide

Includes general FPGA information such as architecture, software, and packaging.

DS557: Spartan-3AN FPGA Data Sheet

Includes ISF and FPGA timing specifications

Also see the Spartan-3AN FPGA Starter Kit for implementation examples, including using the ISF after configuration.

Spartan-3A/3AN FPGA Starter Kit Documentation

UG334: Spartan-3A/3AN FPGA Starter Kit User Guide

Spartan-3A/3AN FPGA Starter Kit Reference Designs





Chapter 2Spartan-3AN FPGA In-System Flash User Guide

In-System Flash Memory Architecture

Block Diagram

The Spartan[®]-3AN FPGA In-System Flash (ISF) memory consists of a main nonvolatile, reprogrammable Flash memory array and one or two SRAM page buffers, as shown in Figure 2-1. The Flash memory array is organized into Pages, Blocks, and Sectors. The smallest erasable unit is a Page. Page size depends on both the device and the addressing mode. The one or two SRAM page buffers simplify system interfaces and data programming. All Spartan-3AN FPGAs, except the XC3S50AN FPGA, have two SRAM page buffers. The XC3S50AN FPGA has a single such buffer.

All accesses to the ISF from the FPGA application are through a four-wire SPI interface, as described in "SPI_ACCESS Design Primitive," page 9.

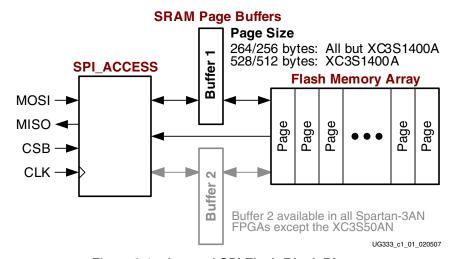


Figure 2-1: Internal SPI Flash Block Diagram

Flash Memory Array

For optimal flexibility, the In-System Flash (ISF) memory is divided into three levels of granularity, as shown in Figure 2-2. Figure 2-2 shows a specific example for the XC3S700AN. Other Spartan-3AN FPGA family members are similar but either have a different number of sectors or a different page size. The number of sectors and page size for other Spartan-3AN FPGAs is listed in Table 2-1, page 18.



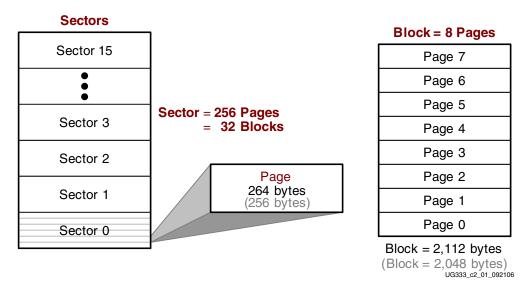


Figure 2-2: XC3S700AN Internal SPI Flash Memory Hierarchy

Table 2-1: Spartan-3AN FPGA Memory Architecture

Device	Total Flash Bits	Sectors	Sector Size	Pages per Sector	Total Pages	Page Size (Bytes)
XC3S50AN	1,081,344 ⁽¹⁾	4 ⁽¹⁾	33K	128	512 ⁽¹⁾	264
XC3S200AN	4,325,376	8	66K		2,048	264
XC3S400AN	4,325,376	8	66K	256	2,048	264
XC3S700AN	8,650,752	16	66K	230	4,096	264
XC3S1400AN	17,301,504	16	132K		4,096	528

Notes:

1. Maximum supported by the Xilinx tools. See "In-System Flash Change," page 14.

The most basic construct within the hierarchy is a memory *Page*. By default, a Page consists of 264 bytes, except on the XC3S1400AN FPGA, which has a larger page size of 528 bytes. The page size is reduced when the Optional Power-of-2 Addressing Mode is selected, as shown in gray in Figure 2-2. The SRAM page buffer(s), shown in Figure 2-1, are large enough to hold an entire page image. A page is the smallest erasable element within the ISF memory, while a byte is the smallest readable and writable element within an SRAM page buffer.

Pages are also grouped into a larger structure called a *Block*, which consists of 8 pages. The Block Erase command provides an intermediate solution between the fast-but-small Page Erase command and the slower-but-larger Sector Erase command. Finally, pages and blocks are further combined into *Sectors*. A sector typically consists of 256 contiguous pages or 32 contiguous blocks, except on the XC3S50AN, which has 128 pages per sector. Sectors have additional control options. Sectors can be selectively write-protected by the FPGA application, a featured called Sector Protection. Similarly, sectors can be permanently locked down, preventing the contents from ever being erased or modified, using a feature called Sector Lockdown. The sector controls similarly affect any data bytes, pages, and blocks within the sector.



The ISF memory hierarchy directly impacts the ISF commands and addressing, as described in subsequent sections.

Sector 0 is further subdivided into two, individually protected sub-sectors, as shown in Figure 2-3. While the combined Sector 0 is the same size as all other sectors, Sector 0a is always 8 pages while Sector 0b represents the remaining pages in Sector 0. Consequently, the commands that operate on Sector 0 require slightly different addressing and control than the same commands used on other sectors.

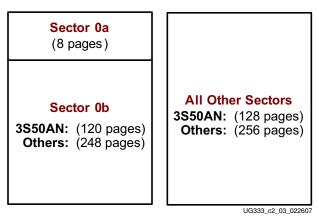


Figure 2-3: Sector 0 is Sub-divided into Two Smaller Sub-sectors

Spartan-3AN FPGA applications generally never make use of the split Sector 0 structure, but applications must be aware that it exists in order to erase or protect Sector 0.

Addressing Overview

All commands that require an address use a 24-bit address field to select a sector, a block, a page, or a byte location within a page. However, the In-System Flash memory supports two different possible addressing schemes.

Addressing Modes

- All Spartan-3AN FPGAs, as delivered, use the Default Addressing Mode, detailed in Table 2-2. All Xilinx® software primarily supports this mode.
- With an additional, special programming step, described in Appendix A, "Optional Power-of-2 Addressing Mode", Spartan-3AN FPGAs support a slightly different addressing mode, which may be more natural for some applications.

The Default Addressing Mode provides roughly 3% more total memory bits. Figure 2-4, page 20 shows the Flash memory array for the XC3S700AN FPGA, plus a detailed, expanded diagram of a page within the Flash array. The diagram also describes how the 24 bits in a command address field select a sector, block, page, or byte within a memory page. Figure 2-5 is a similar diagram specific to the XC3S1400AN, which uses a larger page size.

Using the Default Addressing Mode, each memory page is slightly larger than the typical power-of-2 page size found in other memories. For example, all Spartan-3AN FPGAs except the XC3S1400AN use a 264-byte page, while the XC3S1400AN memory pages are double the size at 528 bytes. The "extra" bits are useful for a variety of applications.

More total nonvolatile memory for FPGA configuration or data storage applications.



- Page pointers, linked address pointers, attributes, and status indicators for a Flashbased file system.
- Error detection/correction bits for extreme applications.
- Counters, to track the number of program/erase cycles per page.

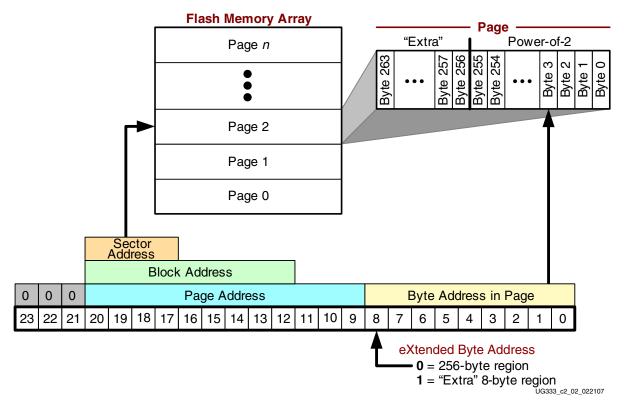


Figure 2-4: Default Addressing Mode for XC3S700AN FPGA



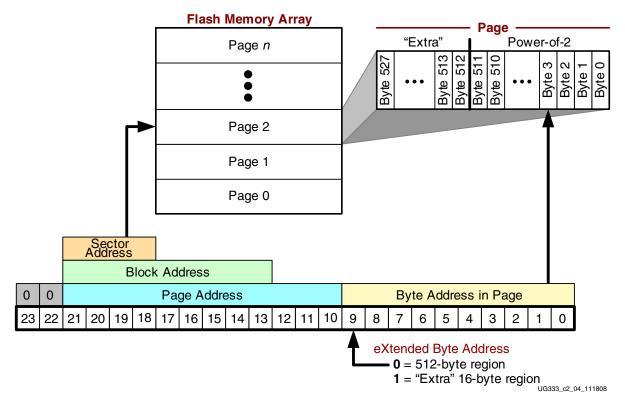


Figure 2-5: Default Addressing Mode, XC3S1400AN FPGA



Default Addressing Mode

In the default addressing mode, specific memory bytes are addressed by page and by the specific byte location within that page. As shown in Table 2-2, the number of pages and the page size varies by FPGA part number.

Table 2-2: Default Addressing Mode

FPGA		ı	Hig	h A	ddr	ess	6		Middle Address Low A						ddr	ess	•							
_	23	22	21	20		18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
3S50AN	0	0	0	0	0	0	Sec	ctor						I	Dor	't C	are	bit	s					
(X-FAB ISF) ⁽¹⁾							SA1	SA0			or 0 or 0		X	X	X	X	Х	X	X	X	X	X	X	X
								Blo	ck A	Add	res	5				I	Don	't C	Care	bit	s			
							BL5	BL4	BL3	BL2	BL1	BL0	х	х	Х	X	Х	X	Х	Х	Х	Х	Х	Х
								Pag	e A	ddr	ess	(512	2 pa	ges))		Byt	e A	ddr	ess	(264	4 by	tes)	
							PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	BA8	BA7	BA6	BA5	BA4	BA3	BA2	BA1	BA0
3S50AN	0	0	0	0	0	S	ecto	or						I	Dor	't C	are	bit	s					
(UMC ISF) ⁽¹⁾						SA2	SA1	SA0			or 0 or 0		X	X	X	X	Х	X	X	X	X	X	X	X
							Bl	lock	Ac	ldre	ess					I	Don	't C	Care	bit	s			
						BL6	BL5	BL4	BL3	BL2	BL1	BL0	Х	х	х	Х	χ	X	х	Х	Х	х	х	Х
												024	pag	es)			Byt	e A	ddr	ess	(264	l 4 by	tes)	
						PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	BA8	BA7	BA6	BA5	BA4	BA3	BA2	BA1	BA0
3S200AN	0	0	0	0	S	ecto											re b							
3S400AN					SA2	SA1	SA0			ctor			Х	Х	Х	Х	Х	X	Х	Х	Х	Х	Х	Х
					3 ,		Bloc	ck A								I	Don	′t C	Care	bit	s			
					BL7				BL3		BL1	BL0	Х	Х	X	Х	Х	X	X	X	X	X	X	х
						Pa	age	Ad	dre	ss (2,04	18 p	age	es)			Byt	e A	ddr	ess	(264	1 by	tes)	
					PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	BA8	BA7	BA6	BA5	BA4	BA3	BA2	BA1	BA0
Bit Location	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
3S700AN	0	0	0		Sec	ctor					•	•		Do	on't	Ca	re b	its						
				SA3	SA2	SA1	SA0			ctor ctor			X	X	X	X	X	X	X	X	X	X	X	Х
						Bl	ock	ock Address				I	Don	′t C	Care	bit	s							
				BL8	BL7	BL6	BL5	BL4	BL3	BL2	BL1	BL0	X	X	X	X	Х	X	X	X	X	X	X	Х
						Pag	ge A	dd	ress	(4,	096	pag	ges)				Byt	e A	ddr	ess	(264	4 by	tes)	
				PA11	PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	BA8	BA7	BA6	BA5	BA4	BA3	BA2	BA1	BA0



Middle Address **Low Address High Address FPGA** 23 22 21 20 19 18 17 16 15 | 14 | 13 | 12 | 11 | 10 | 8 7 4 3 3S1400AN n Sector Don't Care bits SA2 Sector 0a SA1 SA0Χ Χ Χ X Χ Χ Χ Χ χ χ Χ Χ X Sector 0b **Block Address** Don't Care bits BL3 BL0 BL2 BL1 Χ Χ Χ Χ X Χ Χ Χ Χ Χ Χ χ Χ $B\Gamma$ BL BL Page Address (4,096 pages) Byte Address (528 bytes) PA10 PA11 PA9 PA8 PA7 PA6 PA5 PA3 BA9 BA6 BA5 BA4 BA3 BA2 BA0PA4 PA2 PA0BA7 BA1 PAI **Bit Location** 22 21 20 18 17 16 15 14 13 12 11 10 8 19 9 6 3 2

Table 2-2: Default Addressing Mode (Continued)

Notes:

Delivered State

Each Spartan-3AN FPGA is delivered with an erased ISF memory. Engineering Samples may have a pre-programmed pattern, and should be erased and reprogrammed with the FPGA bitstream used in the end application.

- All Flash memory locations are erased and byte locations contain 0xFF.
- Spartan-3AN FPGAs use the "Default Addressing Mode," page 22.
- The "Sector Protection Register," page 78 is programmed with 0x00, indicating that all memory sectors are unprotected.
- The Unique Identifier field in the "Security Register," page 89 is permanently factory programmed with a value that is unique to every Spartan-3AN FPGA.
- The User-Defined Field in the "Security Register," page 89 is erased, and all locations are 0xFF.

Memory Allocation Tables

The following tables describe how the ISF memory is allocated to FPGA configuration bitstreams and the portions that are available for page-aligned and sector-aligned data. The tables assume that the ISF memory contains two FPGA configuration bitstreams, the primary bitstream loaded at power-up and a secondary MultiBoot bitstream, starting at the next sector boundary. If the application does not require a MultiBoot bitstream, then the allocated ISF memory can be used for data storage. The physical address is shown for both the Default Addressing Mode and for the Optional Power-of-2 Addressing Mode. Consequently, the starting page number is different between the addressing modes for any user data that shares a sector with the end of an FPGA configuration bitstream.

- ISF memory allocation for the XC3S50AN FPGA is provided in Table 2-3, page 24.
- ISF memory allocation for the XC3S200AN FPGA is provided in Table 2-4, page 25.
- ISF memory allocation for the XC3S400AN FPGA is provided in Table 2-5, page 26.
- ISF memory allocation for the XC3S700AN FPGA is provided in Table 2-6, page 27.
- ISF memory allocation for the XC3S1400AN FPGA is provided in Table 2-7, page 28.

^{1.} The XC3S50AN with the UMC ISF has 2 Mbits of memory but only 1 Mbit is supported by the Xilinx tools. See "In-System Flash Change," page 14.



Table 2-3: XC3S50AN In-System Flash Memory Allocation

Allocation	Secto	r	Defau	ılt Addressing Mode	_	onal Power-of-2 ressing Mode
			Page	Address	Page	Address
	0	a	0	0x00_0000	0	0x00_0000
Bitstream	U	b		0x00_1000		0x00_0800
	1	1		0x01_9E00	213	0x00_D500
			208	0x01_A000	214	0x00_D600
First available user data space (page aligned)	1					
1 400			255	0x01_FE00	255	0x00_FF00
	2		256	0x02_0000	256	0x01_0000
2nd MultiBoot Bitstream, or available for user data space						
1	3		463	0x03_9E00	469	0x01_D500
			464	0x03_A000	470	0x01_D600
Second available user data space (page aligned) ⁽¹⁾	3					
1 400,			511	0x03_FE00	511	0x01_FF00

Notes:

1. Maximum supported by the Xilinx tools. See "In-System Flash Change," page 14.



Table 2-4: XC3S200AN In-System Flash Memory Allocation

Allocation	Sect	tor	Defau	ult Addressing Mode		nal Power-of-2 ressing Mode		
			Page	Address	Page	Address		
	0	a	0	0x00_0000	0	0x00_0000		
Bitstream	U	b		0x00_1000		0x00_0800		
bitsticant								
	2		566	0x04_6C00	584	0x02_4800		
			567	0x04_6E00	585	0x02_4900		
First available user data space (page aligned)	2			• • •		• • •		
						0x05_FE00	767	0x02_FF00
2nd MultiBoot Bitstream, or	3		768	0x06_0000	768	0x03_0000		
available for user data	•••			• • •		• • •		
space	5		1,334	0x0A_6C00	1,352	0x05_4800		
C d 'l-l-l d-(-			1,335	0x0A_6E00	1,353	0x05_4900		
Second available user data space (page aligned)	5			• • •		• • •		
			1,535	0x0B_FE00	1,535	0x05_FF00		
			1,536	0x0C_0000	1,536	0x06_0000		
	6					• • •		
User data space			1,791	0x0D_FE00	1,791	0x06_FF00		
(sector aligned)			1,792	0x0E_0000	1,792	0x07_0000		
	7							
			2,047	0x0F_FE00	2,047	0x07_FF00		



Table 2-5: XC3S400AN In-System Flash Memory Allocation

Allocation	Sec	tor	Defau	Ilt Addressing Mode	_	nal Power-of-2 ressing Mode
			Page	Address	Page	Address
	0	a	0	0x00_0000	0	0x00_0000
Bitstream	U	b		0x00_1000		0x00_0800
Ditstream						
	3		893	0x06_FA00	921	0x03_9900
	3		894	0x06_FC00	922	0x03_9A00
First available user data space (page aligned)						
1 400			1,023	0x07_FE00	1,023	0x03_FF00
2nd MultiBoot Bitstream, or	4		1,024	0x08_0000	1,024	0x04_0000
available for user data						
space	7		1,917	0x0E_FA00	1,945	0x07_9900
			1,918	0x0E_FC00	1,946	0x07_9A00
Second available user data space (page aligned)	7			• • •		
1 400/			2,047	0x0F_FE00	2,047	0x07_FF00



Table 2-6: XC3S700AN In-System Flash Memory Allocation

Allocation	Sec	tor	Defaul	t Addressing Mode		nal Power-of-2 essing Mode
			Page	Address	Page	Address
	0	a	0	0x00_0000	0	0x00_0000
Bitstream	U	b		0x00_1000		0x00_0800
Ditstream						
	5		1,293	0x0A_1A00	1,334	0x05_3600
			1,294	0x0A_1C00	1,335	0x05_3700
First available user data space (page aligned)	5	•				
1 40 0 7			1,535	0x0B_FE00	1,535	0x05_FF00
2nd MultiBoot Bitstream, or	6		1,536	0x0C_0000	1,536	0x06_0000
available for user data						
space	11	-	2,829	0x16_1A00	2,890	0x0B_4A00
			2,830	0x16_1C00	2,871	0x0B_4B00
Second available user data space (page aligned)	11	-		• • •		
			3,071	0x17_FE00	3,071	0x0B_FF00
			3,072	0x18_0000	3,072	0x0C_0000
	12		•••	• • •		• • •
			3,327	0x19_FE00	3,327	0x0C_FF00
			3,328	0x1A_0000	3,328	0x0D_0000
	13	3				
User data space (sector			3,583	0x1B_FE00	3,583	0x0D_FF00
aligned)			3,584	0x1C_0000	3,584	0x0E_0000
	14	Ŀ	•••			• • •
			3,839	0x1D_FE00	3,839	0x0E_FF00
			3,840	0x1E_0000	3,840	0x0F_0000
	15	5				
			4,095	0x1F_FE00	4,095	0x0F_FF00



Table 2-7: XC3S1400AN In-System Flash Memory Allocation

Allocation	Sector		Defaul	t Addressing Mode		al Power-of-2 essing Mode
			Page	Address	Page	Address
	0	a	0	0x00_0000	0	0x00_0000
Bitstream	U	b		0x00_2000		0x00_1000
Ditstream						
	4		1,125	0x11_9400	1,160	0x09_1000
			1,126	0x11_9800	1,161	0x09_1200
First available user data space (page aligned)	4					• • •
1 40 0 /			1,279	0x13_FC00	1,279	0x09_FE00
2nd MultiBoot Bitstream, or	5		1,280	0x14_0000	1,280	0x0A_0000
available for user data						
space	9		2,405	0x25_9400	2,440	0x13_1000
			2,406	0x25_9800	2,441	0x13_1200
Second available user data space (page aligned)	9	!				• • •
1 40 0 /			2,559	0x27_FC00	2,559	0x13_FE00
			2,560	0x28_0000	2,560	0x14_0000
	10					• • •
			2,815	0x2B_FC00	2,815	0x15_FE00
			2,816	0x2C_0000	2,816	0x16_0000
	11					• • •
			3,071	0x2F_FC00	3,071	0x17_FE00
			3,072	0x30_0000	3,072	0x18_0000
	12	2				
User data space (sector			3,327	0x33_FC00	3,327	0x19_FE00
aligned)			3,328	0x34_0000	3,328	0x1A_0000
	13	3				• • •
			3,583	0x37_FC00	3,583	0x1B_FE00
			3,584	0x38_0000	3,584	0x1C_0000
	14	Ļ				• • •
			3,839	0x3B_FC00	3,839	0x1D_FE00
			3,840	0x3C_0000	3,840	0x1E_0000
	15	5		• • •		
			4,095	0x3F_FC00	4,095	0x1F_FE00



MultiBoot Configuration Bitstream Guidelines

The following guidelines are recommended when storing multiple configuration files in the In-System Flash (ISF) memory.

Align to Flash Sector Boundaries

Spartan-3AN FPGA MultiBoot addressing is flexible enough to allow a bitstream to begin at any byte boundary. However, ideally, a Spartan-3AN FPGA MultiBoot configuration image should be aligned to a sector boundary. This way, one FPGA bitstream can be updated without affecting others in the Flash. Aligning to an ISF sector boundary provides the additional advantage of allowing independent protection or lockdown of the bitstreams.

Additional Memory Space Required for DCM_WAIT

Multiple configuration images should be spaced more than 5 ms apart so that the second configuration file does not interfere with a delayed start-up following programming with the first configuration file. Start-up can be delayed by waiting for lock from one or more Digital Clock Managers (DCMs), a slow or missing STARTUP user clock, or holding the DONE pin Low.

Each DCM provides an option setting that, during configuration, causes the FPGA to wait for the DCM to acquire and lock to its input clock frequency before the DCM allows the FPGA to finish the configuration process. The lock time, which is specified in the Spartan-3AN FPGA data sheet, depends on the DCM mode, and the input clock frequency.

Even if the FPGA is waiting for one or more DCMs to lock before completing configuration, the FPGA's configuration controller continues searching for the next synchronization word. If two adjacent MultiBoot images are placed one immediately following the other, and the first FPGA bitstream contains a DCM with the DCM_WAIT option set, then potential configuration problems can occur. If the controller sees the synchronization word in the second FPGA bitstream before completing the current configuration, it starts interpreting data from the second bitstream. However, the FPGA's configuration logic may complete the current configuration even though the FPGA has read data from the second bitstream.

Caution! FPGA applications that use the DCM_WAIT option on a DCM must ensure sufficient spacing between MultiBoot configuration images!

Spacing MultiBoot bitstreams sufficiently apart in memory prevents the FPGA from ever seeing the second synchronization word. For more details, see <u>UG332: Spartan-3</u> <u>Generation Configuration User Guide</u>, Chapter 14, *Reconfiguration and MultiBoot*.



User Data Storage Guidelines

The following guidelines are recommended when storing user data in the In-System Flash (ISF) memory.

- 1. Do not intermix user data with the last page of FPGA configuration bitstream data. Intermixing user data and configuration data makes updating the FPGA bitstream more difficult.
- 2. If using the Sector Protection or Sector Lockdown features, do not intermix user data in the sectors that contain the FPGA bitstream(s).

See the "Memory Allocation Tables," page 23 for specific locations for each Spartan-3AN FPGA and for both addressing modes.



Read Commands

The Spartan®-3AN FPGA application reads In-System Flash (ISF) memory data either directly from the main Flash memory or from either one of the SRAM data buffers by issuing the appropriate command code. Table 3-1 summarizes and compares the various supported read commands. Some read commands offer multiple forms. One form is best for reading large blocks of contiguous data while the other form is better for reading single bytes from randomly-address locations. Typically, the commands with faster data transfer also have a longer initial latency and require one or more "don't care" bytes after sending the appropriate read command and 24-bit address.

Table 3-1: Summary of In-System Flash Memory Read Commands

Read Command	Best Application	Hex Command Code	Max CLK Frequency	Extra Initial Latency	Read From	Minimum Read Size	Maximum Read Size	Affects SRAM Page Buffers	Simulation Support
Fast Read	Reading a large block of contiguous data, if CLK frequency is above 33 MHz	0x0B	50	8 cycles	Flash array	1 byte	Entire array	No	Yes
Random Read	Reading bytes from randomly-addressed locations, all read operations at 33 MHz or less	0x03	33	None	Flash array	1 byte	Entire array	No	Yes
Page to Buffer Transfer	Transfers the entire contents of a selected ISF memory page to the specified SRAM page buffer	Buffer 1 (0x53) Buffer 2 (0x55)	33	None	SRAM page buffer	One page	One page	Yes	Yes
Buffer Read	Reading multiple contiguous bytes from the SRAM page buffer	Buffer 1 (0xD4) Buffer 2 (0xD6)	50	8 cycles	SRAM page buffer	1 byte	One page	No	No
Buffer Read (Low Freq)	Randomly reading bytes from the SRAM page buffer	Buffer 1 (0xD1) Buffer 2 (0xD3)	33	None	SRAM page buffer	1 byte	One page	No	No

Notes:

1. The Buffer 2 commands are not available in the XC3S50AN because it has only one SRAM page buffer.



Fast Read

The Fast Read command is best for longer, sequential read operations. This is the same command that the FPGA issues during configuration. This command is also best for code shadowing applications, where the FPGA application copies a large amount of code or data into external SRAM or DDR SDRAM for a MicroBlaze™ processor. Although it has longer initial latency than the Random Read command, the Fast Read command supports a CLK clock frequency up to 50 MHz.

The Fast Read command sequentially reads a continuous stream of data directly from Flash memory bypassing the SRAM page buffers, as shown in Figure 3-1. The command specifies an initial starting byte address in the ISF memory. The ISF memory incorporates an internal address pointer that automatically increments on every clock cycle, allowing one continuous read operation without requiring additional address sequences.

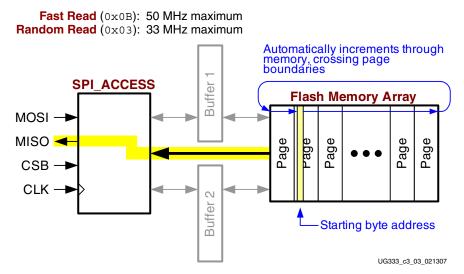


Figure 3-1: Fast Read and Random Read Commands

To perform a Fast Read command, summarized in Table 2-2, page 22 and shown in detail in Figure 3-2, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the Fast Read command code, 0x0B, most-significant bit first.

Table 3-2: Fast Read (0x0B) Command Summary

	Command	24-bit Star	ting Page and By	te Address	Don't Care	ISF Mem	ory D	ata Bytes
Pin	Command	High Address	Middle Address	Low Address	Byte	Byte (most-significant bi		nt bit first)
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5			Byte n+6
MOSI	0x0B		Addressing: See Table 2-2, page 22 Power-of-2 Addressing: See page 95			XX		XX
MISO			High			Data Byte +0		Data Byte +n

Notes:

1. The Fast Read command is supported in simulation.



- Similarly, serially clock in a 24-bit page and byte starting address.
 - The starting byte location can be anywhere in the ISF memory array, located on any page, as shown in Figure 3-1.
 - If using default addressing, see Table 2-2, page 22.
 - If using power-of-2 addressing, see Table A-3, page 95.

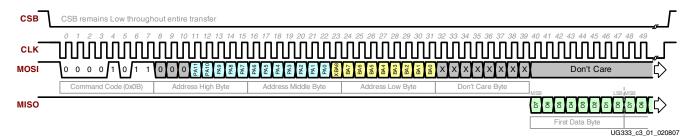


Figure 3-2: Fast Read Command Waveform (XC3S700AN, Default Address Mode)

- Provide eight additional CLK cycles. At this point, the data supplied on the MOSI input does not matter.
- On the next falling CLK edge, the requested data serially appears on the MISO output port.
 - Data is clocked out serially, most-significant bit first.
 - While CSB is Low, new data appears on the MISO output on every subsequent falling CLK edge. The ISF memory automatically increments the implied address counter through contiguous memory locations, as highlighted in Figure 3-1, regardless of the address mode.
- To end the data transfer, deassert CSB High on the falling edge of CLK.

The CSB signal must remain Low throughout the entire data transfer—when writing the command code, the 24 address bits, the 8 "don't care" bits, and when reading the dummy bytes and data bytes.

Upon reaching the end of a memory page, the ISF memory continues reading at the beginning of the next page, as shown in Figure 3-1. There is no added delay when crossing a page boundary. After reading the last bit in the memory array, the ISF continues reading but returns to the beginning of the first page of memory. Again, there is no added delay when wrapping around from the end of the array to the beginning of the array. A Low-to-High transition on CSB terminates the read operation and the MISO output pin returns High. See "In-System Flash Change," page 14 for special wrapping considerations for the XC3S50AN.

The Fast Read command bypasses both SRAM page buffers; the contents of the buffers remain unchanged.

Random Read

The Random Read command is best for smaller, random read operations. It has less initial latency than the Fast Read command, but only operates up to 33 MHz, less than the maximum frequency possible with the Fast Read command.

The Random Read command sequentially reads a continuous stream of data directly from Flash memory bypassing the SRAM page buffers, as shown in Figure 3-1. The command specifies an initial starting byte address in the ISF memory. The ISF memory incorporates



an internal address pointer that automatically increments on every clock cycle, allowing one continuous read operation without requiring additional address sequences.

To perform a Random Read command, summarized in Table 3-3 and shown in detail in Figure 3-3, the FPGA application must perform the following actions.

Table 3-3: Random Read (0x03) Command Summary

	Command	24-bit Sta	arting Page and Byte	Address	ISF Mem	ISF Memory Data			
Pin	Command	High Address	Middle Address	Low Address	(most-signifi	nifica	ficant bit first)		
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5		Byte n+5		
MOSI	0x03		g: See Table 2-2, page -2 Addressing: See T		XX		XX		
MISO			High		Data Byte +0		Data Byte +n		

Notes:

- 1. The Random Read command is supported in simulation.
 - Drive CSB Low while CLK is High or on the rising edge of CLK.
 - On the falling edge of CLK, serially clock in the Random Read command code, 0x03, most-significant bit first.
 - Similarly, serially clock in a 24-bit starting byte address.
 - The starting byte location can be anywhere in the ISF memory array, located on any page, as shown in Figure 3-1.
 - If using the default address scheme, see Table 2-2, page 22.
 - ♦ If using power-of-2 addressing, see Table A-3, page 95.

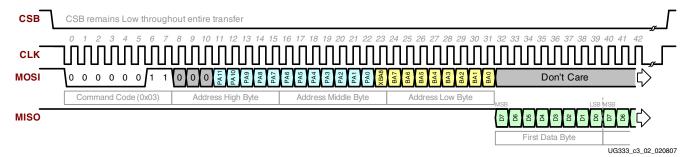


Figure 3-3: Random Read Command Waveform (XC3S700AN, Default Address Mode)

- No dummy byte is required for the Random Read command. At this point, the data supplied on the MOSI input does not matter.
- On the next falling CLK edge, the requested data serially appears on the MISO output port.
 - Data is clocked out serially, most-significant bit first.
 - While CSB is Low, new data appears on the MISO output on every subsequent falling CLK edge. The ISF memory automatically increments the implied address counter through contiguous memory locations, as highlighted in Figure 3-1, regardless of the address mode.
- To end the data transfer, deassert CSB High on the falling edge of CLK.



The CSB signal must remain Low throughout the entire data transfer—when writing the command code, the 24 address bits, and when reading the data bytes.

Upon reaching the end of a memory page, the ISF memory continues reading at the beginning of the next page, as shown in Figure 3-1. There is no added delay when crossing a page boundary. After reading the last bit in the memory array, the ISF continues reading but returns to the beginning of the first page of memory. Again, there is no added delay when wrapping around from the end of the array to the beginning of the array. A Low-to-High transition on CSB terminates the read operation and the MISO output pin returns High.

The Fast Read command bypasses both SRAM page buffers; the contents of the buffers remain unchanged.

Page to Buffer Transfer

The Page to Buffer Transfer command copies the entire contents of an ISF memory page into the specified SRAM page buffer, as shown in Figure 3-4. The contents of the ISF memory page are unaffected.

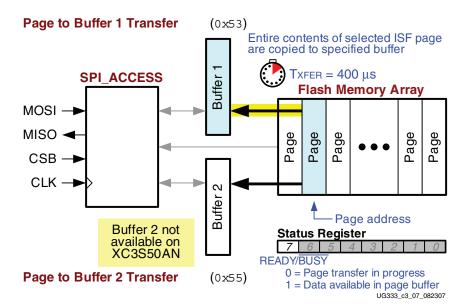


Figure 3-4: Page to Buffer Transfer Command

To issue a Page to Buffer Transfer command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate Page to Buffer Transfer command code, shown in Table 3-4, most-significant bit first.



Table 3-4: Page to Buffer Transfer Command Summary

			24-bit Page Address	
Dia	Command	High Address	Middle Address	Low Address
Pin		ISF Page	Address	Byte Address Unused
	Byte 1	Byte 2	Byte 3	Byte 4
	Page to Buffer 1	Default Addressing: See Tab	ole 5-3, page 55	
MOSI	Transfer 0x53	Power-of-2 Addressing: See	Table A-3, page 95	Don't Care
MOSI	Page to Buffer 2 Transfer ⁽¹⁾ 0x55			XX

Notes:

- 1. The Buffer 2 command is not available in the XC3S50AN because it has only one SRAM page buffer.
- 2. The Page to Buffer Transfer command is supported in simulation.
 - Similarly, serially clock in a 24-bit page address.
 - Only the Page Address is required. Any byte address values are ignored.
 - ♦ If using the default address scheme, see Table 2-2, page 22.
 - If using power-of-2 addressing, see Table A-3, page 95.
 - To end the data transfer, deassert CSB High on the falling edge of CLK. Subsequently, the entire contents of the addressed ISF memory page is transferred to the selected SRAM page buffer.

The page transfer operation is internally self-timed and does not require CLK to toggle. The page is transferred in 400 μs or less, specified as symbol T_{XFER} in the Spartan-3AN FPGA data sheet and shown in Table 3-5. During the transfer, the READY/BUSY bit (bit 7) in the Status Register is '0' and returns to '1' when the transfer completes. The FPGA application can monitor this bit to determine when the transfer is complete or the application can wait 400 μs or more before accessing the data in the specified SRAM page buffer.

Table 3-5: Page to Buffer Transfer, T_{XFER}

Symbol	Description	FPGA	Max	Units
T _{XFER}	Page to Buffer Transfer Time	All	400	μs

While the page transfer is in progress, the FPGA can access any other portion of the ISF memory that is not actively involved in the transfer, including any of the following commands.

- Read from or write to the other SRAM page buffer, not involved in the present operation.
 - Buffer Read
 - Buffer Write
- Status Register Read
- Information Read

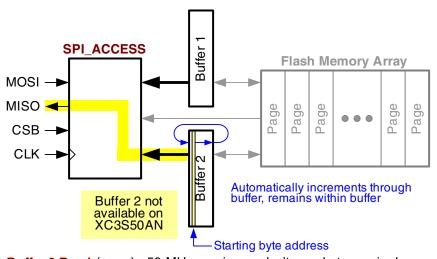


Buffer Read

The FPGA application can independently access the SRAM data buffers separately from the ISF memory array, as shown in Figure 3-5. The Buffer Read command sequentially reads data directly from the selected buffer. When reading data from the buffer, first load data into the buffer from an ISF memory page using the Page to Buffer Transfer command.

Caution! The Buffer 2 Read command is not supported on the XC3S50AN FPGA because it contains only one buffer.

Buffer 1 Read (0xD4): 50 MHz maximum, don't care byte required Buffer 1 Read (0xD1): 33 MHz maximum



Buffer 2 Read (0xD6): 50 MHz maximum, don't care byte required

Buffer 2 Read (0xD3): 33 MHz maximum

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Figure 3-5: Buffer Read Command

There are two versions of the Buffer Read command. The version that operates up to 50 MHz, shown in Table 3-6, is best for reading multiple contiguous bytes from the SRAM page buffer. This command requires eight "don't care" bits after specifying the 24-bit address.

Table 3-6: Buffer Read Command Summary (High Frequency, up to 50 MHz)

		24-b	24-bit Starting Byte Address					
Pin	Command	High Address	Middle Address	Low Address	Don't Care	Page Buffer Data Bytes (most-significant bit first)		
Pin		Unused	Byte Address in Buffer		Byte	(meet eigimeem zit mei,		
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6		Byte n+6
MOSI	Buffer 1 Read 0xD4	000	Default Addressing: See Table 2-2, page 22 Power-of-2 Addressing: See Table A-3, page 95		XX	VV		VV
MOSI	Buffer 2 Read ⁽¹⁾ 0xD6	0x00			AA	XX	•	XX
MISO			High			Data Byte +0		Data Byte +n

Notes:

- 1. The Buffer 2 Read command is not available in the XC3S50AN because it has only one SRAM page buffer.
- 2. The Buffer Read command (High Frequency) is not supported in simulation.



The slower version that operates up to 33 MHz, shown in Table 3-7, is best for reading single, randomly-accessed bytes within the SRAM page buffer. This version has lower initial latency for single-byte transfers.

Table 3-7: Buffer Read Command Summary (Low Frequency, up to 33 MHz)

		24-bi	Iress					
Pin	Command	High Address	Middle Address	Low Address	Page Buffer Data Bytes (most-significant bit first)			
Pili		Unused	sed Byte Address in Buffer		(
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5		Byte 6	
MOSI	Buffer 1 Read 0xD1 Buffer 2 Read ⁽¹⁾	0x00	Default Addressing: See Table 2-2, page 22 Power-of-2 Addressing: See		XX		XX	
MISO	0xD3	Hid	Table A-3, page 95	Data Byte 10		Data Byte +n		
IVIISU		High			Data Byte +0	•••	Data byte +n	

Notes:

- 1. The Buffer 2 Read command is not available in the XC3S50AN because it has only one SRAM page buffer.
- 2. The Buffer Read command (Low Frequency) is not supported in simulation.

It is possible for the FPGA application to read from one SRAM page buffer while the other buffer is actively transferring data to the main memory from a previous programming operation, as shown in Figure 3-6.

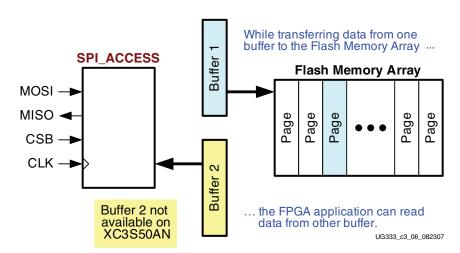


Figure 3-6: SRAM Page Buffers Support Read-while-Write Operations

To issue a Buffer Read command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate Buffer Read command code, shown in either Table 3-6 or Table 3-7, most-significant bit first.
- Similarly, serially clock in a 24-bit starting byte address. The page address bits are ignored.
 - The starting byte location can be anywhere in the ISF memory array, located on any page, as shown in Figure 3-5.



- If using the default address scheme, see Table 2-2, page 22.
- If using power-of-2 addressing, see Table A-3, page 95.
- The slower version of the command (Table 3-7) does not require "don't care" bits while the faster version (Table 3-6) of the command does require eight "don't care" bits. At this point, the data supplied on the MOSI input does not matter.
- On the next falling CLK edge, the requested data serially appears on the MISO output port.
 - Data is clocked out serially, most-significant bit first.
 - While CSB is Low, new data appears on the MISO output on every subsequent falling CLK edge. The ISF memory automatically increments the implied address counter through contiguous memory locations, as highlighted in Figure 3-5, regardless of the address mode.
- To end the data transfer, drive CSB High on the falling edge of CLK.

The CSB signal must remain Low throughout the entire data transfer. If the transaction reaches the end of a buffer, the ISF memory continues reading back at the beginning of the buffer.





Write and Program Commands

The Spartan®-3AN FPGA application programs data into the In-System Flash (ISF) memory either directly to the main Flash memory array or through one of the SRAM page buffers by issuing the appropriate command code. Table 4-1 summarizes and compares the various supported write and program commands. One form is best for writing large blocks of contiguous data while the other form is better for writing single bytes to randomly-addressed locations. Typically, the commands with faster data transfer also have a longer initial latency and require one or more "don't care" bytes after sending the appropriate write command and 24-bit address.

Table 4-1: Summary of Write and Program Commands

Command	Best Application	Hex Command Code	Maximum CLK Frequency	Erase Page	Write To	Minimum Write Size	Maximum Write Size	Affects SRAM Page Buffers	Simulation Support
Buffer Write	Write data to SRAM page buffer; when complete, transfer to ISF memory using Buffer to Page Program command	Buffer 1 (0x84) Buffer 2 ⁽¹⁾ (0x87)	50	No	SRAM page buffer	1 byte	One page	Yes	Yes
Buffer to Page Program with Built- in Erase	First erases selected memory page and programs page with data from designated buffer	Buffer 1 (0x83) Buffer 2 ⁽¹⁾ (0x86)	50	Yes	ISF page	One page	One page	No	Yes
Buffer to Page Program without Built-in Erase	Program a previously erased page with data from designated buffer	Buffer 1 (0x88) Buffer 2 ⁽¹⁾ (0x89)	50	No	ISF page	One page	One page	No	Yes
Page Program Through Buffer	Combines Buffer Write with Buffer to Page Program with Built-in Erase command	Buffer 1 (0x82) Buffer 2 ⁽¹⁾ (0x85)	50	Yes	Selected buffer first, ISF page later	1 byte	One page	Yes	Yes
Page to Buffer Compare (Program Verify)	Verify that the ISF memory array was programmed correctly	Buffer 1 (0x60) Buffer 2 ⁽¹⁾ (0x61)	50	No	N/A	N/A	N/A	No	Yes



Table 4-1: Summary of Write and Program Commands (Continued)

Command	Best Application	Hex Command Code	Maximum CLK Frequency	Erase Page	Write To	Minimum Write Size	Maximum Write Size	Affects SRAM Page Buffers	Simulation Support
Auto Page Rewrite	Refresh page contents after 10,000 random program operations to a sector	Buffer 1 (0x58) Buffer 2 ⁽¹⁾ (0x59)	50	Yes	Buffer, then page	N/A	N/A	Yes	No

1. The Buffer 2 commands are not available in the XC3S50AN because it has only one SRAM page buffer.

Buffer Write

The FPGA application can write data directly to one of the SRAM page buffers. Along with the Buffer Read command, the FPGA application can randomly read or write the buffer data without affecting the ISF memory array. Data is not written into nonvolatile Flash memory using this command. Once the data within the buffer is finalized, the FPGA application can subsequently copy contents of the buffer into the ISF memory array using one of the following commands.

- Buffer to Page Program with Built-in Erase
- Buffer to Page Program without Built-in Erase

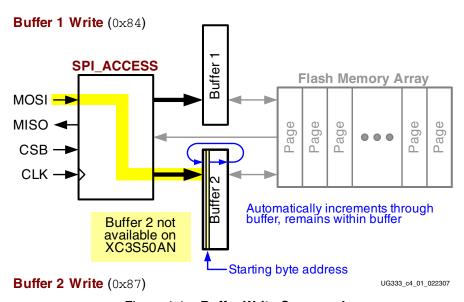


Figure 4-1: Buffer Write Command

To issue a Buffer Write command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate Buffer Write command code, shown in Table 4-2, most-significant bit first.



rabio i	asie 72. Bandi Wild Commany									
		24-bit Starting Byte Address								
D:	Command	High Address	Middle Address	Low Address	ow Address Page Buffer Data		ta			
Pin		Unused	Byte Address in Buffer							
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6		Byte n+4		
	Buffer 1 Write		Default Addressing: See Table 2-2, page 22 Power-of-2 Addressing: See Table A-3, page 95							
MOSI	0x84	0x00			Data +0	Data +1		Data +n		
MOSI	Buffer 2 Write ⁽¹⁾	0.00			Data +0					
	0x87									

Table 4-2: Buffer Write Command Summary

- 1. The Buffer 2 Write command is not available in the XC3S50AN because it has only one SRAM page buffer.
- 2. The Buffer Write command is supported in simulation.
 - Similarly, serially clock in a 24-bit starting byte address. Any page address information is ignored.
 - The starting byte location can be anywhere within the selected SRAM page buffer, as shown in Figure 4-1.
 - If using the default address scheme, see Table 2-2, page 22.
 - If using power-of-2 addressing, see Table A-3, page 95.
 - On the next falling CLK edge, serially supply the write data on the MOSI port.
 - Data is clocked in serially, most-significant bit first.
 - While CSB is Low, present new data on the MOSI pin on every subsequent falling CLK edge. The ISF memory automatically increments the implied address counter through the SRAM page buffer, as highlighted in Figure 4-1.
 - The first data byte written is stored in Byte Address + 0
 - The second data byte written is stored in Byte Address + 1, and so on.
 - If the transaction reaches the end of a buffer, the ISF memory continues writing back at the beginning of the buffer.
 - To end the data transfer, drive CSB High on the falling edge of CLK.

The CSB signal must remain Low throughout the entire data transfer.

Buffer to Page Program with Built-in Erase Buffer to Page Program without Built-in Erase

The ISF memory offers two similar commands that copy the contents of an SRAM page buffer to a selected memory page. One version erases the selected memory page before programming the page, while the second version programs a previously-erased page with data from an SRAM page buffer.

The Buffer to Page Program with Built-in Erase command, shown in Figure 4-2, first
erases the selected memory page and then programs the page with the data stored in
the designated SRAM page buffer.



Buffer 1 to Page Program with Erase (0x83) Selected ISF page is first erased, then programmed with Buffer data TPEP = 35 to 40 msSPI_ACCESS Buffer Flash Memory Array MOSI -Page Page Page Page Page Page MISO Page CSB -CLK -Q Buffer Page address This command will not erase or program a page within a sector that is protected by Sector Protect or Sector Lockdown **Status Register** 7 6 5 READY/BUSY

Buffer 2 to Page Program with Erase (0x86)

1 = Selected page now erased/programmed 5) UG333_c4_02_082307

0 = Page Erase and Program in progress

Figure 4-2: Buffer to Page Program with Built-in Erase

• The **Buffer to Page Program without Built-in Erase** command, shown in Figure 4-3, simply programs an erased page with the data stored in the designated SRAM page buffer.

Buffer 1 to Page Program without Erase (0x88) Buffer data is written to an erased page. TPP = 4 to 6 msSPI_ACCESS Buffer Flash Memory Array MOSI -Page Page Page Page Page MISO ade CSB -CLK -S Buffer Page address This command will not program a page within a sector that is protected by Sector Protect or Sector Lockdown Status Register 0 = Page programming in progress Buffer 2 not available on XC3S50AN 1 = Page programming complete

Figure 4-3: Buffer to Page Program without Built-in Erase

To issue a Buffer to Page Program command, with or without built-in erase, the FPGA application must perform the following actions.

Drive CSB Low while CLK is High or on the rising edge of CLK.

Buffer 2 to Page Program without Erase (0x89)

• On the falling edge of CLK, serially clock in the appropriate command code, shown in Table 4-3, most-significant bit first.

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Table 4-3: Buffer to Page Program Command Summary

			24-bit Page Addres	ss	
Pin	Command	High Address	Middle Address	Low Address	
PIII		Page Addre	Page Address in Buffer		
	Byte 1	Byte 2	Byte 3	Byte 4	
	Buffer 1 to Page Program with Erase 0x83	Default Addressing See Table 5-3, page 5	,	Don't Care XX	
MOSI	Buffer 2 to Page Program with Erase ⁽¹⁾ 0x86	Power-of-2 Address See Table A-4, page			
IVIOSI	Buffer 1 to Page Program without Erase 0x88				
	Buffer 2 to Page Program without Erase ⁽¹⁾ 0x89				

- 1. The Buffer 2 commands are not available in the XC3S50AN because it has only one SRAM page buffer.
- 2. The Buffer to Page Program command is supported in simulation.
 - Similarly, serially clock in a 24-bit page address.
 - If using the default address scheme, see Table 2-2, page 22 or Table 5-3, page 55.
 - If using power-of-2 addressing, see Table A-4, page 96.
 - To end the data transfer, drive CSB High on the falling edge of CLK.

The CSB signal must remain Low throughout the entire data transfer.

A Low-to-High transition on the CSB input completes the command.

- If using the command *with* page erase...
 - the ISF memory first erases the selected memory page
 - then programs the page with the data stored in the designated SRAM page buffer.
 - The operation is internally self-timed and completes in the Page Erase and Programming time, T_{PEP}, shown in Table 4-4 and specified in the <u>Spartan-3AN</u> FPGA data sheet.

Table 4-4: Page Erase and Programming Time, T_{PEP}

Symbol	Description	FPGA	Max	Units
$T_{ m PEP}$	Page Erase and Programming Time.	XC3S50AN XC3S200AN XC3S400AN XC3S700AN ⁽¹⁾	35	ms
		XC3S1400AN	40	ms

Notes:

1. XC3S700AN T_{PEP} Max is 55 ms for devices with ISF from UMC (XCN14003).



- If using the command without page erase...
 - The ISF memory programs the page with the data stored in the designated SRAM page buffer.
 - This version of the command does not erase the selected page.
 - ◆ The operation is internally self-timed and completes in the Page Programming time, T_{PP}, shown in Table 4-5 and specified in the <u>Spartan-3AN FPGA data sheet</u>.

Table 4-5: Page Programming Time, T_{PP}

Symbol	Description	FPGA	Max	Units
T_{PP}	Page Programming Time	XC3S50AN XC3S200AN XC3S400AN	4	ms
		XC3S700AN XC3S1400AN	6	ms

During the command execution time, the READY/BUSY bit (bit 7) of the Status Register indicates whether the Page Programming or Page Erase and Programming operation is in progress or whether it has completed.

Page Program Through Buffer

This operation combines the Buffer Write (Figure 4-1) and Buffer to Page Program with Built-in Erase (Figure 4-2) operations. The FPGA application must specify a full 24-bit address, including both the Page Address and the starting Byte Address within the SRAM page buffer.

To issue a Page Program Through Buffer command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate Page Program Through Buffer command code, shown in Table 4-2, most-significant bit first.

Table 4-6: Page Program Through Buffer Command Summary

	Command	24-bit Page	Page Ruffer Date					
Pin		High Address	ligh Address Middle Address Low Addres			Page Buffer Data		
	Byte 1	Byte 2	Byte 2 Byte 3 Byte 4			Byte 6		Byte n+4
MOSI	Page Program Through Buffer 1 0x82 Page Program Through Buffer 2 ⁽¹⁾ 0x85		sing: See Table 2- dressing: See Tabl		Data +0	Data +1		Data +n

Notes:

- 1. The Buffer 2 command is not available in the XC3S50AN because it has only one SRAM page buffer.
- 2. The Page Program Through Buffer command is supported in simulation.



- Similarly, serially clock in a 24-bit starting page and byte address.
 - The starting byte location can be anywhere within the selected SRAM page buffer, as shown in Figure 4-1.
 - The page address must also be specified.
 - If using the default address scheme, see Table 2-2, page 22.
 - If using power-of-2 addressing, see Table A-3, page 95.
- On the next falling CLK edge, serially supply the write data on the MOSI port.
 - Data is clocked in serially, most-significant bit first.
 - While CSB is Low, present new data on the MOSI pin on every subsequent falling CLK edge. The ISF memory automatically increments the implied address counter through the SRAM page buffer, as highlighted in Figure 4-1.
 - The first data byte written is stored in Byte Address + 0
 - The second data byte written is stored in Byte Address + 1, and so on.
 - If the transaction reaches the end of a buffer, the ISF memory continues writing back at the beginning of the buffer.
 - While it is possible to write less than a full page of data, be sure that the SRAM page buffer contains valid data. The data from any unwritten buffer locations will write the previous contents to the ISF memory page.
- To end the data transfer, drive CSB High on the falling edge of CLK.

The CSB signal must remain Low throughout the entire data transfer. A Low-to-High transition on the CSB input completes the command.

The ISF memory first erases the selected memory page, then programs the page with the data stored in the designated SRAM page buffer. The operation is internally self-timed and completes in the Page Erase and Programming time, T_{PEP} , shown in Table 4-4 and specified in the Spartan-3AN FPGA data sheet.

During the command execution time, the READY/BUSY bit (bit 7) of the Status Register indicates whether the Page Erase and Programming operation is in progress or whether it has completed.



Page to Buffer Compare (Program Verify)

The Page to Buffer Compare command is not actually a programming command, but is primarily used to verify correct programming of nonvolatile data in an ISF memory page. As shown in Figure 4-4, this command compares the contents of the addressed memory page against the contents of the designated SRAM page buffer. If one or more bits differ between the page and buffer, then the Compare bit (bit 6 in the Status Register) is '1'.

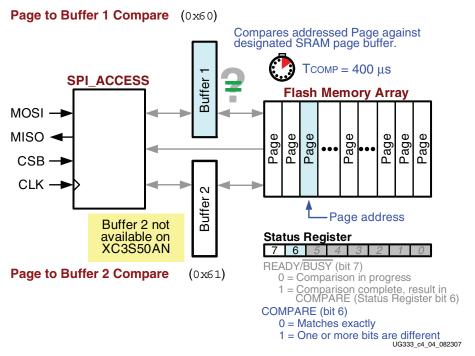


Figure 4-4: Page to Buffer Compare Command

To issue a Page to Buffer Compare command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate command code, shown in Table 4-2, most-significant bit first.

Table 4-7: Page to Buffer Compare Command Summary

	Command	24-bit Page Address					
Pin	Command	High Address Middle Addres		Low Address			
	Byte 1	Byte 2	Byte 2 Byte 3				
MOSI	Page to Buffer 1 Compare 0x60	Default Addressin See Table 5-3, page	Don't Care				
IVIOSI	Page to Buffer 2 Compare ⁽¹⁾ 0x61	Power-of-2 Addressing: See Table A-4, page 96		XX			

Notes:

- 1. The Buffer 2 command is not available in the XC3S50AN because it has only one SRAM page buffer.
- 2. The Page to Buffer Compare command is supported in simulation.



- Similarly, serially clock in a 24-bit Page Address.
 - If using the default address scheme, see Table 2-2, page 22.
 - If using power-of-2 addressing, see Table A-4, page 96.
- To end the command, drive CSB High on the falling edge of CLK.

The CSB signal must remain Low throughout the entire data transfer. A Low-to-High transition starts the comparison between the addressed ISF memory page and the designated SRAM page buffer. The operation is internally self-timed and completes in a Page to Buffer Compare time, shown in Table 4-8 and specified in the Spartan-3AN FPGA data sheet.

Table 4-8: Page to Buffer Compare Time, T_{COMP}

Symbol	Description	FPGA	Max	Units
T _{COMP}	Page to Buffer Compare Time	All	400	μs

During the command execution time, the READY/BUSY bit (bit 7) of the Status Register indicates whether the Page to Buffer Compare operation is in progress or whether it has completed.

When the operation completes, the Status Register bit 6, Compare, reflects the result of the comparison.

Pre-initializing SRAM Page Buffer Contents

The SRAM page buffers are not automatically pre-initialized to a known value before executing a command. Consequently, never assume the contents of a buffer location. Instead, the FPGA application must define each location.

The fastest way to pre-initialize a buffer is using the Buffer Write command. Ideally, define any blank locations to 0xFF, which is the erased state of an ISF memory location.

Another easy method to pre-initialize a page buffer is to use an Page to Buffer Transfer command, pointed at a page that is known to be erased. This method copies the blank page, which contains all 0xFF, into the page buffer. Although this method takes more time to complete, about $400 \, \mu s$, it has less overhead for the FPGA application.



EEPROM-Like, Byte-Level Write Operations

The Spartan-3AN FPGA In-System Flash (ISF) memory includes small page size, SRAM page buffers, combined with flexible memory read and write commands. Consequently, the ISF memory can perform small, byte-level write operations, much like EEPROM memories.

To update one or more bytes without affecting other Flash data, perform these steps.

- Copy the contents of an entire ISF memory page to an SRAM page buffer using the Page to Buffer Transfer command.
- Update one or more locations in the SRAM page buffer.
 - If updating one byte or contiguous bytes, use a Page Program Through Buffer command, which automatically erases and programs the addressed page at the completion of the command.
 - If updating multiple, non-contiguous bytes, update selected locations in the page buffer using multiple Buffer Write commands. When the buffer updates are complete, issue a Buffer to Page Program with Built-in Erase command.
- If randomly updating data, each page within a sector must be updated/rewritten at least once every 10,000 cumulative page erase or page programming operations in that sector. Instead of tracking the number of operations, optionally issue a Auto Page Rewrite command after updating each page.

Sequential vs. Random Page Programming, Cumulative Operations

In most applications, the ISF memory stores nonvolatile data such as FPGA bitstreams and MicroBlazeTM processor code. In these applications, entire memory sectors are first erased, then new programming data is written to each page sequentially. In these applications, where data is programmed sequentially, each page supports up to 100,000 program/erase cycles.

In other applications, the FPGA application may store or update nonvolatile data in randomly-addressed page locations. One such example is described in "EEPROM-Like, Byte-Level Write Operations". While each page still supports a maximum of 100,000 program/erase cycles, each page within a randomly-addressed sector must be refreshed every 10,000 cumulative page erase/program operations with that sector. Refreshing the page contents avoids any potential charge buildup due to the random page programming operations.

The ISF memory has a special command, Auto Page Rewrite, specifically for this purpose.



Auto Page Rewrite

This command is only needed if multiple bytes within a page or multiple pages of data are modified in a random fashion within a sector. This command combines two other operations, a Page to Buffer Transfer command followed by a Buffer to Page Program with Built-in Erase command, as shown in Figure 4-5.

Auto Page Rewrite (Buffer 1) (0x58) Updates/rewrites selected page. TPEP = 35 to 40 msSPI_ACCESS lash Memory Array MOSI -Page Page Page MISO Page CSB CLK · N Buffer: Page address Buffer 2 not **Status Register** available on XC3S50AN READY/BUSY (bit 7) Auto Page Rewrite (Buffer 2) (0x59) 0 = Rewrite in progress 1 = Rewrite complete

UG333_c4_05_082307

Figure 4-5: Auto Page Rewrite Command

- 1. A page of data is first copied from the addressed ISF memory page to either Buffer 1 or Buffer 2.
- 2. Then, the same data from Buffer 1 or Buffer 2 is programmed back to the same ISF memory page.

To issue an Auto Page Rewrite command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate Auto Page Rewrite command code, shown in Table 4-2, most-significant bit first.



Table 4-9: Auto Page Rewrite Through Buffer Command Summary

	Command	24-bit Page Address				
Pin	Command	High Address	Middle Address	Low Address		
	Byte 1	Byte 2	Byte 3	Byte 4		
MOSI	Auto Page Rewrite (Buffer 1) 0x58	Default Addres See Table 5-3, pa	Don't Care			
IVIOSI	Auto Page Rewrite (Buffer 2) ⁽¹⁾ 0x59	Power-of-2 Add See Table A-4, p	XX			

- 1. The Buffer 2 command is not available in the XC3S50AN because it has only one SRAM page buffer.
- 2. The Auto Page Rewrite Through Buffer command is not supported in simulation.
- Similarly, serially clock in a 24-bit Page Address.
 - If using the default address scheme, see Table 2-2, page 22.
 - If using power-of-2 addressing, see Table A-4, page 96.
- To end the data command, drive CSB High on the falling edge of CLK.

A Low-to-High transition on the CSB input completes the command.

The addressed ISF memory page is then copied into the designated buffer, the memory page is erased, then the buffer contents are copied back to the addressed page. The operation is internally self-timed and completes in the Page Erase and Programming time, T_{PEP}, shown in Table 4-4 and specified in the Spartan-3AN FPGA data sheet.

During the command execution time, the READY/BUSY bit (bit 7) of the Status Register indicates whether the Auto Page Rewrite operation is in progress or whether it has completed.



Erase Commands

The Spartan®-3AN FPGA In-System Flash (ISF) memory supports multiple levels of erase operations for maximum application flexibility.

- The Page Erase command erases the smallest possible unit, a single ISF memory page.
- The Block Erase command erases a group of eight pages.
- The Sector Erase command erases all the pages within an ISF memory sector.

Sector Protect and Sector Lockdown Prevent Erase Operations

The Sector Protection and Sector Lockdown features prevent accidental or unauthorized erase operations. A page, block, or sector erase command will not occur if the operation targets a location within a sector that is actively protected via the Sector Protection or Sector Lockdown features.

Erased State

Erase commands erase the selected page, block, or sector and return the contents to a logical '1', or 0xFF on a byte basis. Erase commands do not affect the contents of any page, block or sector in a protected or locked down sector.



Page Erase

The Page Erase command erases any individual page in the ISF memory array, as shown in Figure 5-2. Typically, the Page Erase command is used to prepare a page for a subsequent Buffer to Page Program without Built-in Erase command.

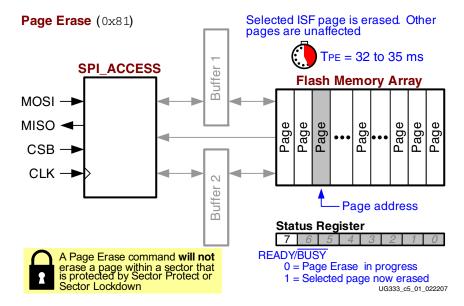


Figure 5-1: Page Erase Command

To perform a Page Erase command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate Page Erase command code, 0x81, most-significant bit first, as shown in Table 5-1.

24-bit Address **High Address** Middle Address Low Address Command Pin **Byte Address** Page Address Unused Byte 4 Byte 1 Byte 2 Byte 3 **Default Addressing:** See Table 5-3 Don't Care **MOSI** 0x81 Optional Power-of-2 Addressing: See XXTable A-4, page 96

Table 5-1: Page Erase (0x81) Command

Notes:

- 1. The Page Erase command is supported in simulation.
- Similarly, serially clock in a 24-bit page address.
 - Only the page address is required. Any byte address values are ignored.
 - The number of pages and the alignment of the page address within the 24-bit address field varies by Spartan-3AN FPGA type, as shown in Table 5-2.



- If using the default address scheme, see Table 5-3.
- If using power-of-2 addressing, see Table A-4, page 96.
- Drive CSB High on the falling edge of CLK to end the command.

Table 5-2: Page Addressing Summary

		Addressing Mode									
FPGA	Total	D	efault	Power-of-2							
	Pages	Page Size (Bytes)	Alignment	Page Size (Bytes)	Alignment						
XC3S50AN	512 ⁽¹⁾										
XC3S200AN XC3S400AN	2,048	264	Every 512 bytes	256	Every 256 bytes						
XC3S700AN	4,096										
XC3S1400AN	4,096	528	Every 1K bytes	512	Every 512 bytes						

1. Maximum supported by the Xilinx tools. See "In-System Flash Change," page 14.

Table 5-3: Page Address, Default Addressing Mode

FPGA			Hig	h A	ddr	ess	3			M	lido	lle A	Add	ires	SS				Lov	v A	ddr	ess	;	
II GA	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
3S50AN ⁽¹⁾	0	0	0	0	0	0		Pag	e A	ddr	ess	(512	2 pa	ges))			Do	on't	Ca	re b	its		
(X-FAB ISF)							PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	Х	X	X	X	X	X	X	X	Х
3S50AN ⁽¹⁾	0	0	0	0	0	F	age	Ad	dre	ss (1,02	4 p	ages	s)				Do	on't	Ca	re b	its		
(UMC ISF)						PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	X	X	X	X	X	X	X	X	X
3S200AN	0	0	0	0		P	Page Address (2,048 pages)				Don't Care bits													
3S400AN					PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	X	х	X	x	x	X	X	X	х
3S700AN	0	0	0			Pag	ge A	dd	ress	s (4,	096	pag	ges))		Don't Care bits								
				PA11	PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	x	х	X	x	x	X	X	X	х
3S1400AN	0	0			Pag	ge A	e Address (4,096 pages)]	Don	't C	are	bits	3							
			PA11	PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0	x	x	x	X	x	x	X	X	X	x
Bit Location	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0

Notes:

1. The XC3S50AN with the UMC ISF has 2 Mb of memory but only 1 Mb is supported by the Xilinx tools. See "In-System Flash Change," page 14.

A Low-to-High transition on the CSB input completes the command and the Flash then erases the selected page. The erase operation is internally self-timed and completes in the time shown in Table 5-4 and specified in the Spartan-3AN FPGA data sheet. During this time, the READY/BUSY bit (bit 7) of the Status Register indicates whether the Page Erase operation is in progress or whether it has completed.



Table 5-4: Page Erase Time

Symbol	Description	FPGA	Max	Units
T_{PE}	Page Erase Time	XC3S50AN XC3S200AN XC3S400AN	32	ms
		XC3S700AN ⁽¹⁾ XC3S1400AN	35	ms

1. XC3S700AN T_{PE} Max is 50 ms for devices with the ISF from UMC (see XCN14003).

While the Page Erase operation is in progress, the FPGA can access any other portion of the ISF memory, including any of the following commands.

- Read from or write to an SRAM page buffer, which are not used during an erase operation.
 - Buffer Read
 - ♦ Buffer Write
- Status Register Read
- Information Read

Block Erase

The Block Erase command erases eight pages at one time, as shown in Figure 5-2, which proves useful when writing large amounts of data into the ISF memory. The Block Erase command avoids using multiple Page Erase commands, resulting in a faster erase time for between three to eight ISF pages.

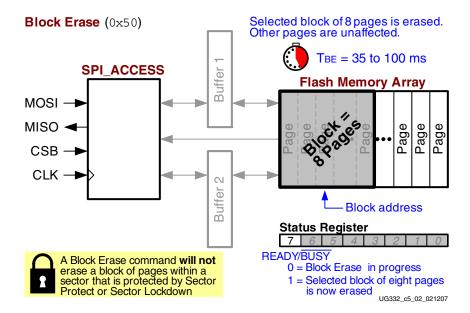


Figure 5-2: Block Erase Command



To perform a Block Erase command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate Block Erase command code, 0x50, most-significant bit first, as shown in Table 5-5.

Table 5-5: Block Erase (0x50) Command

			24-bit Address								
Pin	Command	High Address	Middle Address	Low Address							
FIII		Block A	Byte Address Unused								
	Byte 1	Byte 2	Byte 3	Byte 4							
MOSI	0x50	Optional Power-of- Table A-5, page 96		Don't Care XX							

Notes:

- 1. The Block Erase command is not supported in simulation.
- Similarly, serially clock in a 24-bit block address.
 - Only the block address is required.
 - The block address is always aligned to every 8 pages. It does not span across just any block of eight contiguous pages.
 - The number of blocks and the alignment of the block address within the 24-bit address field varies by Spartan-3AN FPGA type, as shown in Table 5-6.
 - If using the default address scheme, see Table 5-7.
 - ◆ If using power-of-2 addressing, see Table A-5, page 96.
- Drive CSB High on the falling edge of CLK to end the command.

Table 5-6: Block Addressing Summary

			Addressi	ng Mode				
FPGA	Total	De	fault	Power-of-2				
	Blocks	Block Size (Bytes)	Alignment	Block Size (Bytes)	Alignment			
XC3S50AN	64 ⁽¹⁾							
XC3S200AN XC3S400AN	256	2,112 (2K+64)	Every 8 pages Every 4K bytes	2,048 (2K)	Every 8 pages Every 2K bytes			
XC3S700AN	512							
XC3S1400AN	512	4,224 (4K+128)	Every 8 pages Every 8K bytes	4,096 (4K)	Every 8 pages Every 4K bytes			

Notes:

 $1. \ \ Maximum \ supported \ by \ the \ Xilinx \ tools. \ See \ "In-System Flash \ Change," \ page \ 14.$



Low Address High Address Middle Address FPGA 23 22 21 20 19 18 17 16 15 14 13 12 11 10 9 8 7 6 5 4 3 2 1 0 0 3S50AN⁽¹⁾ 0 0 **Block Address** Don't Care bits (X-FAB ISF) BL4 BL0 BL1 Χ Χ Χ Χ Χ Χ Χ Χ Χ Χ Χ BI BI BI $3S50AN^{(1)}$ 0 0 0 **Block Address** Don't Care bits (UMC ISF) BL6 BL4 BL3 BL2 BL0 Χ Χ Χ Χ Χ Χ Χ Χ Χ Χ Χ Χ BL. BI 3S200AN 0 0 0 0 **Block Address** Don't Care bits 3S400AN BL6 BL7 BL5 BL4 BL3 BL2 Χ χ χ Χ Χ Χ Χ Χ Χ Χ Χ BL 3S700AN 0 **Block Address** Don't Care bits BL5 BL8 BL4 BL3 BL2 BL0Χ χ Χ Χ Χ Χ Χ χ Χ Χ Χ 3S1400AN Don't Care bits 0 **Block Address** BL5 BL8 BL7 BL6 BL4 BL3 BL2

Table 5-7: **Block Addressing, Default Addressing Mode**

Χ χ χ Χ Χ Χ Χ Χ Χ Χ Χ Χ

BL1

A Low-to-High transition on the CSB input completes the command and the Flash then erases the selected block of 8 pages. The erase operation is internally self-timed and completes in the time shown in Table 5-8 and specified in the Spartan-3AN FPGA data sheet. During this time, the READY/BUSY bit (bit 7) of the Status Register indicates whether the Block Erase operation is in progress or whether it has completed.

Table 5-8: Block Erase Time

Symbol	Description	FPGA	Max	Units
T _{BE}	Block Erase Time	XC3S50AN	35	ms
		XC3S200AN XC3S400AN	75	ms
		XC3S700AN XC3S1400AN	100	ms

While the Block Erase operation is in progress, the FPGA can access any other portion of the ISF memory, including any of the following commands.

- Read from or write to an SRAM page buffer, which are not used during an erase operation.
 - **Buffer Read**
 - **Buffer Write**
- Status Register Read
- Information Read

^{1.} The XC3S50AN with the UMC ISF has 2 Mb of memory but only 1 Mb is supported by the Xilinx tools. See "In-System Flash Change," page 14.



Sector Erase

The Sector Erase command erases any unprotected, unlocked sector in the main memory, as shown in Figure 5-3. Only one sector can be erased at one time.

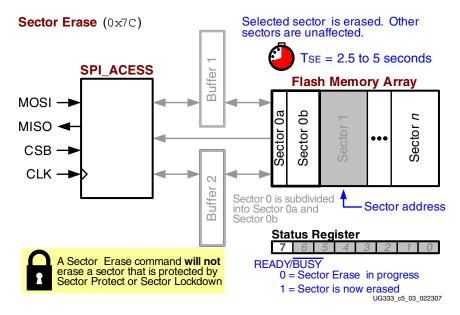


Figure 5-3: Sector Erase Command

To perform a Sector Erase command, the FPGA application must perform the following actions.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the appropriate Block Erase command code, 0x7C, most-significant bit first, as shown in Table 5-9.

Table 5-9: Sector Erase (0x7C) Command

	24-bit Address									
Command	High Address	High Address Middle Address								
	Block A	Byte Address Unused								
	Default Addressing: Se	ee Table 5-10								
0x7C	Optional Power-of-2 A Table A-6, page 97	Don't Care XX								
	Full Address Map , incl locations: See Table 5-11		AA							

Notes:

- 1. The Sector Erase command is supported in simulation.
- Similarly, serially clock in a 24-bit sector address.
 - Sector 0 is different than all other sectors.
 - Sector 0 is subdivided into two subsectors called Sector 0a and Sector 0b.
 - Sector 0a and Sector 0b are each erased individually and require a unique address with additional addressing bits, different than all the other sectors.



- The page address and byte address bits, which follow the Sector Address, specify any valid address location within the sector which is to be erased.
- If using the default address scheme, see Table 5-10.
- ◆ If using power-of-2 addressing, see Table A-6, page 97.
- ♦ When erasing a sector, be aware of how the FPGA bitstream is stored within the ISF memory. There is always one bitstream stored starting at Sector 0, as indicated in blue in Table 5-11 and Table 5-12, page 62. If using MultiBoot configuration, a second FPGA bitstream is stored starting on the next sector boundary, following the first bitstream. The optional MultiBoot bitstream is shown in yellow in Table 5-11 and Table 5-12, page 62.
- Drive CSB High on the falling edge of CLK to end the command.

Sector Addressing

The addressing to access a sector depends on the address mode.

- "Default Addressing Mode," page 60
- "Optional Power-of-2 Addressing Mode," page 93

Furthermore, Table 5-11 and Table 5-12, page 62 summarize the sector addresses for each Spartan-3AN FPGA and also indicate where the FPGA configuration bitstream is stored.

Also see "Memory Allocation Tables," page 23.

Default Addressing Mode

Table 5-10 shows the sector addressing for default addressing mode. Sector 0 is subdivided into two subsectors, designated as Sector 0a and Sector 0b. These subsectors require additional address bits.



Table 5-10: Sector Addressing, Default Addressing Mode

FPGA /	Sector			Hig	jh A	ddr	ess				N	Mido	dle /	Add	res	s				Lov	ΝA	ddr	ess		
I F GA /	Sector	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
XC3S50AN ⁽¹⁾	Sector	0	0	0	0	0	0	Sec	ctor							Dor	ı't C	are	bits	;					
(X-FAB ISF)	Sector 0a							0	0	0	0	0	0	X	X	X	X	X	X	X	Χ	X	X	X	X
	Sector 0b	Ī											1												
	Sectors 1–3							SA1	SA0	Х	Χ	X	X	X	X	X	X	X	X	X	X	X	X	Χ	X
XC3S50AN ⁽¹⁾	Sector	0	0	0	0	0	S	Secto	r							Dor	ı't C	are	bits	3					
(UMC ISF)	Sector 0a	Ī					0	0	0	0	0	0	0	X	X	X	X	X	Χ	X	Χ	X	X	Χ	X
	Sector 0b												1												
	Sectors 1–7						SA2	SA1	SA0	X	X	X	Х	X	Х	Х	X	X	Х	Х	Х	Х	X	X	X
XC3S200AN	Sector	0	0	0	0	S	ecto	or							D	on't	Caı	re bi	ts						
XC3S400AN	Sector 0a					0	0	0	0	0	0	0	0	X	X	X	X	X	X	Χ	Χ	X	X	X	X
	Sector 0b												1												
	Sectors 1–7					SA2	SA1	SA0	X	Х	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X
XC3S700AN	Sector	0	0	0		Sec	ctor			-					D	on't	Caı	re bi	ts						
	Sector 0a				0	0	0	0	0	0	0	0	0	X	X	X	X	X	X	X	Χ	X	X	X	X
	Sector 0b												1												
	Sectors 1–15				SA3	SA2	SA1	SA0	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X
XC3S1400AN	Sector	0	0		Sec	ctor				Don't Care bits															
	Sector 0a			0	0	0	0	0	0	0	0	0	X	X	Х	X	X	X	X	X	Χ	X	X	X	X
	Sector 0b											1													
	Sectors 1–15			SA3	SA2	SA1	SA0	Х	Х	Χ	X	Х	Х	X	Х	Х	Χ	Х	Х	Х	X	Х	Х	X	Х

 $^{1. \ \ \, \}text{The XC3S50AN with the UMC ISF has 2 Mb of memory but only 1 Mb is supported by the Xilinx tools. See "In-System Flash Change," page 14.}$



Table 5-11: XC3S50AN, XC3S200AN, XC3S400AN Sector Boundaries

_	Spartan-3AN XC3S50AN FPGA					XC3S2	200AN	XC3S4	400AN		
Pages	oer S	ector	12	28	Page		25	56			
Add	ressir	ng	Default	Power-of-2		Default	Power-of-2	Default	Power-of-2		
Sector /	Size	Page	264	256		264	256	264	256		
0	0a	0	0x00_0000	0x00_0000	0	0x00_0000	0x00_0000	0x00_0000	0x00_0000		
U	0b	8	0x00_1000	0x00_0800	8	0x00_1000	0x00_0800	0x00_1000	0x00_0800		
1		128	0x01_0000	0x00_8000	256	0x02_0000	0x01_0000	0x02_0000	0x01_0000		
2		256	0x02_0000	0x01_0000	512	0x04_0000	0x02_0000	0x04_0000	0x02_0000		
3		384	0x03_0000	0x01_8000	768	0x06_0000	0x03_0000	0x06_0000	0x03_0000		
4			Note 1	Note 1	1,024	0x08_0000	0x04_0000	0x08_0000	0x04_0000		
5		_	Note 1	Note 1	1,280	0x0A_0000	0x05_0000	0x0A_0000	0x05_0000		
6		_	Note 1	Note 1	1,536	0x0C_0000	0x06_0000	0x0C_0000	0x06_0000		
7		_	Note 1	Note 1	1,792	0x0E_0000	0x07_0000	0x0E_0000	0x07_0000		

 XC3S50AN sectors 4–7 for devices with ISF from UMC are not supported by the Xilinx tools. See "In-System Flash Change," page 14.

Table 5-12: XC3S700AN, XC3S1400AN Sector Boundaries

	rtan-3 FPGA		XC3S7	700AN	XC3S1	400AN
Pages	per S	Sector		2	56	
Add	dress	ing	Default	Power-of-2	Default	Power-of-2
Sector /	Size	Page	264	256	528	512
0	0a	0	0x00_0000	0x00_0000	0x00_0000	0x00_0000
	0b	8	0x00_1000	0x00_0800	0x00_2000	0x00_1000
1		256	0x02_0000	0x01_0000	0x04_0000	0x02_0000
2		512	0x04_0000	0x02_0000	0x08_0000	0x04_0000
3		768	0x06_0000	0x03_0000	0x0C_0000	0x06_0000
4		1,024	0x08_0000	0x04_0000	0x10_0000	0x08_0000
5		1,280	0x0A_0000	0x05_0000	0x14_0000	0x0A_0000
6		1,536	0x0C_0000	0x06_0000	0x18_0000	0x0C_0000
7		1,792	0x0E_0000	0x07_0000	0x1C_0000	0x0E_0000
8		2,048	0x10_0000	0x08_0000	0x20_0000	0x10_0000
9		2,304	0x12_0000	0x09_0000	0x24_0000	0x12_0000
10		2,560	0x14_0000	0x0A_0000	0x28_0000	0x14_0000
11		2,816	0x16_0000	0x0B_0000	0x2C_0000	0x16_0000
12		3,072	0x18_0000	0x0C_0000	0x30_0000	0x18_0000
13	13 3,328		0x1A_0000	0x0D_0000	0x34_0000	0x1A_0000
14	14 3,584		0x1C_0000	0x0E_0000	0x38_0000	0x1C_0000
15		3,840	0x1E_0000	0x0F_0000	0x3C_0000	0x1E_0000

Default Bitstream

Optional MultiBoot Bitstream



Operation Timing

A Low-to-High transition on the CSB input completes the command and the Flash then erases the selected block of 8 pages. The erase operation is internally self-timed and completes in the time shown in Table 5-13 and specified in the Spartan-3AN FPGA data-sheet. During this time, the READY/BUSY bit (bit 7) of the Status Register indicates whether the Sector Erase operation is in progress or whether it has completed.

Table 5-13: Sector Erase Time

Symbol	Description	FPGA	Max	Units
T_{SE}	Sector Erase Time	XC3S50AN	2.5	seconds
		XC3S200AN XC3S400AN XC3S700AN XC3S1400AN	5	seconds

While the Sector Erase operation is in progress, the FPGA can access any other portion of the ISF memory, including any of the following commands.

- Read from or write to an SRAM page buffer, which are not used during an erase operation.
 - Buffer Read
 - Buffer Write
- Status Register Read
- Information Read





Status and Information Commands

The Spartan®-3AN FPGA In-System Flash (ISF) memory provides status and information using two different commands.

- The Status Register provides status about the current state and configuration of the ISF memory.
- The Information Read provide JEDEC-compatible device information.

Status Register

Table 6-1: Status Register Contents (Byte 1)

Bit	7	6	5	4	3	2	1	0
Name	READY/ BUSY	COMPARE		ISF Men	nory Size		SECTOR PROTECT	PAGE SIZE
Description	0 = Busy	0 = Matches	0011 = 1	Mbit: XC3S	50AN (X-FA	AB ISF) ⁽¹⁾	0 = Open	0 = Extended
	1 = Ready	1 = Different	0101 = 2	Mbit: XC3S	50AN (UM	C ISF) ⁽¹⁾	1 = Protected	(Default)
			0111 = 4	Mbit: XC3S	200AN or X	C3S400AN		1 = Power-of-2
			1001 = 8	Mbit: XC3S	700AN			
			1011 = 16	Mbit: XC3	S1400AN			

Notes:

1. See "In-System Flash Change," page 14.

As shown in Table 6-1, the Status Register describes...

- whether the ISF memory is ready to receive additional commands or is busy completing the current command
- the result of a Page to Buffer Compare (Program Verify) command
- the size of the ISF memory array
- whether Sector Protection is presently enabled or not
- the current addressing mode, and consequently the size of each memory page



In the Spartan-3AN FPGAs with the ISF from the UMC fab (see "In-System Flash Change," page 14), the Status register has a second byte (see Table 6-2). For impact on the read command, see "Status Register Read," page 69.

Table 6-2: Status Register Contents, Byte 2 (UMC ISF Only(1))

Bit	7	6	5	4	3	2	1	0
Name	READY/ BUSY	RESERVED	ERASE or PROGRAM ERROR	RESERVED	SECTOR LOCKDOWN ENABLED	PROGRAM SUSPEND BUFFER 2	PROGRAM SUSPEND BUFFER 1	ERASE SUSPEND
Description	0 = Busy 1 = Ready	0	0 = Successful 1 = Error	0	0 = Disabled 1 = Enabled	0 = Not Suspended 1 = Suspended	0 = Not Suspended 1 = Suspended	0 = Not Suspended 1 = Suspended

Notes:

1. See "In-System Flash Change," page 14.



READY/BUSY

READY/BUSY status of the In-System Flash (ISF) memory is indicated by bit 7 in the Status Register, as defined in Table 6-3.

Table 6-3: READY/BUSY (Status Register Bit 7)

READY/BUSY	Description
0	BUSY: The ISF memory is busy completing a command that accesses the internal array. Even while the ISF memory is busy, the FPGA application can issue select commands, as described below.
1	READY: The ISF memory is ready to accept any command. Any previous commands have completed.

There are several commands that cause a busy condition.

- Page to Buffer Transfer
- Page to Buffer Compare (Program Verify)
- Buffer to Page Program with Built-in Erase
- Buffer to Page Program without Built-in Erase
- Page Program Through Buffer
- Page Erase
- Block Erase
- Sector Erase
- Information Read
- Auto Page Rewrite

Even while the ISF memory is busy, the FPGA application can potentially issue the following commands.

- Read from or write to an SRAM page buffer that is not involved in the present operation.
 - Buffer Read
 - Buffer Write
- Status Register Read
- Information Read



Compare

The result of the most recent Page to Buffer Compare command is indicated by bit 6 in the Status Register, as defined in Table 6-4.

Table 6-4: COMPARE (Status Register Bit 6)

COMPARE	Description
0	The data stored in the ISF memory page specified by the most-recent Page to Buffer Compare (Program Verify) command matches the data stored in the specified SRAM page buffer.
1	One or more bits differ between the data stored in the ISF memory page and the SRAM page buffer specified by the most-recent Page to Buffer Compare (Program Verify) command.

ISF Memory Size

The Status Register bits 5:2 indicate the size of the ISF memory array, as defined in Table 6-5. This memory density code is different from the code used in the JEDEC device ID information, shown in Table 6-12, page 73.

Table 6-5: ISF Memory Size (Status Register Bits 5, 4, 3, and 2)

	Status Re	gister Bits	3	Momony Sizo	Associated EDCA(s)	
5	4	3	2	Memory Size	Associated FPGA(s)	
0	0	1	1	1 Mbit	XC3S50AN ⁽¹⁾ (X-FAB ISF)	
0	1	0	1	2 Mbit	XC3S50AN ⁽¹⁾ (UMC ISF)	
0	1	1	1	4 Mbit	XC3S200AN XC3S400AN	
1	0	0	1	8 Mbit	XC3S700AN	
1	0	1	1	16 Mbit	XC3S1400AN	

Notes:

Sector Protect

Bit 1 in the Status Register indicates whether Sector Protection is presently enabled or disabled, as defined in Table 6-6. When enabled, the designated sectors specified in the Sector Protection Register are protected against all programming and erase operations.

Table 6-6: SECTOR PROTECT (Status Register Bit 1)

SECTOR PROTECT	Description				
0	All memory locations open for program and erase commands.				
1	All programming and erase commands are prevented to ISF memory locations within the Sectors defined in the Sector Protection Register.				

The Sector Protect bit does not indicate whether any sectors are locked down. To determine if any sectors are locked down, issue a Sector Lockdown Register Read command.

^{1.} Only 1 Mbit is supported by the Xilinx tools. See "In-System Flash Change," page 14.



Page Size

Bit 0 in the Status Register indicates the size of each ISF memory page and the addressing mode to access data within the ISF memory array, as defined in Table 6-7.

Table 6-7: PAGE SIZE (Status Register Bit 0)

PAGE SIZE	Addressing Mode	FPGA	Page Size
0	Default Addressing Mode	XC3S50AN XC3S200AN XC3S400AN XC3S700AN	264
		XC3S1400AN 528	528
1	Optional Power-of-2 Addressing Mode	XC3S50AN XC3S200AN XC3S400AN XC3S700AN	256
		XC3S1400AN	512

Status Register Read

The FPGA application can read the Status Register at any time, including during any internally self-timed program or erase operation. To read the Status Register, the FPGA application must perform the following operations using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in Status Register Read command code, 0xD7, most-significant bit first.

Table 6-8: Status Register Read (0xD7) Command

Pin	Command	Read Status Byte				
	Byte 1	Byte 2		Byte n		
MOSI	0xD7	XX		XX		
MISO	High	Status Byte		Most-recent Status Byte		

Notes:

- 1. The Status Register Read command is supported in simulation.
- On the clock cycle following the last bit of the command code, the ISF memory
 presents the Status Register byte value on the SPI_ACCESS MISO pin.
 - Clock out the eight status bits, most-significant bit first.
 - While CSB is Low, the continuously updated Status Register value is repeated every eight CLK clock cycles. For example, this capability allows the FPGA application to continuously monitor the READY/BUSY bit of the Status Register until it returns to '1'.
- To end the data transfer, drive CSB High on the falling edge of CLK. The CSB control
 can be deasserted at any time as the command does not require the FPGA application
 to read the entire Status Register value.

See also Figure 1-3, page 12 for an example waveform for this command.



After the ISF receives a Status Register Read (0xD7) command, the ISF outputs the Status Register byte 1 (Table 6-1). If the ISF receives additional CLK cycles with CSB held Low, then the X-FAB ISF again outputs an updated Status Register byte 1. However, for additional CLK cycles following the initial Status Register byte 1, the UMC ISF issues the Status Register byte 2 (Table 6-2) before it repeats an updated output of the Status Register bytes 1 and 2. Thereafter, the ISF repeats the output of its Status Register byte(s) accordingly. Note that bit 7 from all Status Register bytes is always the READY/BUSY status (see "READY/BUSY," page 67).

For compatibility between X-FAB ISF and UMC ISF, the application should do one of the following when repeatedly polling for updated status:

- For every instance of a status check, restart the status read with a new CSB High-to-Low edge, issue a new Status Register Read command, and read only byte 1.
- If only interested in the READY/BUSY status, start the status read with a CSB Highto-Low edge, issue a Status Register Read command, and continuously read status bytes from ISF, but check only the Bit 7 READY/BUSY status (and ignore all other bits in each status byte).



Information Read

The ISF memory supports JEDEC standards to enable systems and software to electronically query and identify the device while it is in system. The ISF Information Read command complies with the JEDEC method, "Manufacturer and Device ID Read Methodology for SPI Compatible Serial Interface Memory Devices." This method identifies various attributes about the Flash memory, including the following information.

- Memory manufacturer
- Vendor-specific device family identifier
- The vendor-specific device identifier for the specified family
- The number of bits stored per memory cell
- The product version
- The number of additional Extended Device Information bytes.

To read the ISF Information, the FPGA application must perform the following operations using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the Information Read command code, 0x9F, most-significant bit first.

Table 6-9: Information Read Command

Pin	Command	JEDEC Manufacturer and Device Identifier						
	Command	Manufacturer ID Dev		ce ID	Extended Info			
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5			
MOSI	0x9F	XX	XX	XX	XX			
MISO	High	0x1F	Family Code/Memory Density Code	0x00	0x00 ⁽²⁾			

Notes:

- 1. The information read command bytes and values shown in the table are supported in simulation.
- XCN14003 describes a change from X-FAB to UMC for all ISF. For only the X-FAB ISF, the extended info byte 5 value is 0x00. For only the UMC ISF, the extended info byte 5 value is 0x01. See Table 6-14 and Table 6-15 for details.

Caution! Ignore the "Byte 5" value for compatibility between ISF memories manufactured at X-FAB and at UMC facilities.

- On the clock cycle following the last bit of the command code, the ISF memory
 presents the first byte of the ISF Information value on the SPI_ACCESS MISO output
 pin.
 - Clock out each information byte, most-significant bit first.
 - The first byte ("Byte 2" shown in Table 6-9) contains the Manufacturer ID, as shown in Table 6-11.
 - The next two bytes ("Byte 3" and "Byte 4"shown in Table 6-9) contain the Device ID, as shown in Table 6-12 and Table 6-13.
 - ◆ The next byte ("Byte 5" shown in Table 6-9) specifies the Extended Device Information string length. For only devices with the X-FAB ISF, the extended info byte 5 value is 0x00 indicating that no additional information follows. For only devices with the UMC ISF, the extended info byte 5 value is 0x01 indicating that



one additional byte of information follows. As indicated in the JEDEC standard, reading the Extended Device Information String Length and any subsequent data is optional.

To end the data transfer, drive CSB High on the falling edge of CLK. The CSB control
can be deasserted at any time and does not require the FPGA application to read the
entire ISF Information value.

The Spartan-3AN In-System Flash memory is architecturally similar to the Adesto DataFlash SPI Flash memories, as shown in Table 6-10. Consequently, the ISF Information relates to the Adesto DataFlash product family.

Table 6-10: Spartan-3AN ISF Memory and Similar Adesto DataFlash Memory

Charten 24N FDC4	Similar Adesto Da	ataFlash Memory	
Spartan-3AN FPGA	X-FAB	UMC	
XC3S50AN ⁽¹⁾	AT45DB011D	AT45DB021E	
XC3S200AN	AT45DB041D	AT45DB041E	
XC3S400AN	- A143DB041D	A143DB041E	
XC3S700AN	AT45DB081D	AT45DB081E	
XC3S1400AN	AT45DB161D	AT45DB161E	

Notes:

Manufacturer Identifier

The first byte of the ISF Information, shown in Table 6-11, provides the JEDEC-assigned manufacturer code. This byte is identical for all Spartan-3AN FPGAs. The JEDEC identifier for the ISF memory is 0x1F. This value is different than the JEDEC code for Xilinx, which is 0x49. The Spartan-3AN FPGA product identifier is available via JTAG.

Table 6-11: First Byte: Manufacturer Identifier

FPGA		JEDEC Assigned Code (0x1F)							
	7	6	5	4	3	2	1	0	
All	0	0	0	1	1	1	1	1	

^{1.} XCN14003 describes a change from X-FAB to UMC for all ISF memories, and from 1 Mb to 2 Mb ISF memory in the XC3S50AN TQ(G)144 devices. See "In-System Flash Change," page 14.



Family Code/Memory Density Code

The second byte includes a portion of the device identifier, as shown in Table 6-12.

- The three-bit **Family Code** is set to binary 001.
- The five-bit **Memory Density Code** indicates the size of ISF memory array and differs between various FPGA densities, as shown in Table 6-12. This value differs from the Status Register density code, shown in Table 6-5, page 68.

Table 6-12: Second Byte: Device Identifier (Part 1 of 2)

FPGA	F	amily Co	de		Memoi	ry Density	y Code	
FFGA	7 6 5		5	4	3	2	1	0
XC3S50AN ⁽¹⁾ (X-FAB ISF) (1 Mbit)				0	0	0	1	0
XC3S50AN ⁽¹⁾ (UMC ISF) (2 Mbit)				0	0	0	1	1
XC3S200AN (4 Mbit)	0	0	1	0	0	1	0	0
XC3S400AN (4 Mbit)				O		1	O	U
XC3S700AN (8 Mbit)				0	0	1	0	1
XC3S1400AN (16 Mbit)				0	0	1	1	0

Notes:

Memory Type/Product Version Code

The third byte includes the remainder of the device identifier, as shown in Table 6-13.

- The three-bit **Multi-Level Cell (MLC) Code** is binary 000, indicating that one bit is stored per memory cell.
- The five-bit **Product Version Code** indicates the ISF revision. This value is currently binary 00000, but can change in future revisions.

Table 6-13: Third Byte: Device Identifier (Part 2 of 2)

FPGA	Multi-	Level Cel	l Code		Produ	Product Version Code					
FFGA	7	6	5	4	3	2	1	0			
All	0	0	0	0	0	0	0	0			

^{1.} See "In-System Flash Change," page 14.



Extended Device Information Field

As noted in $\underline{XCN14003}$, the in-system flash (ISF) memory for the Spartan-3AN FPGA devices is transitioning from wafer fabrication facility X-FAB (0.13 µm process) to UMC (0.11 µm process). The number of optional extended device information (EDI) bytes is different between the X-FAB ISF and UMC ISF. The X-FAB ISF has no additional EDI bytes and the UMC ISF has one additional byte. The details of the EDI bytes and values for each ISF are defined in Table 6-14 and Table 6-15.

The fourth byte (byte 5 shown in Table 6-9) returned from the ISF for the information read command specifies the Extended Device Information (EDI) string length. For only devices with the X-FAB ISF, this fourth byte value is 0×00 indicating that no additional information follows. See Table 6-14 for this fourth byte value from the X-FAB ISF.

Table 6-14: Fourth Byte: EDI String Length (X-FAB ISF)

FPGA			Byte Count (Optional to Read)						
FPGA	7	6	5	4	3	2	1	0	
All, with ISF from X-FAB	0	0	0	0	0	0	0	0	

For the devices with ISF from UMC, the Extended Device Information field is set to 0x01, as shown in Table 6-15, indicating that one byte of EDI data follows. As indicated in the JEDEC Standard, reading the EDI String Length and any subsequent data is optional.

Table 6-15: Fourth and Fifth Bytes: EDI String Length and String (UMC ISF)

FPGA	Byte											
FFGA	7	6	5	4	3	2	1	0				
	Fourth Byte: Byte Count (Optional to Read)											
All, with ISF	0	0	0	0	0	0	0	1				
from UMC	Fifth Byte: EDI (Optional to Read)											
	0	0	0	0	0	0	0	0				

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Power Management

The Spartan®-3AN FPGA In-System Flash (ISF) memory consumes power on the 3.3V V_{CCAUX} power rail to the Spartan-3AN FPGA. Note that write commands are not allowed until 20 ms after VCCAUX has reached at least 2.5V. In general the ISF adds no significant current to the FPGA current. Standby power consumption is approximately 100 μ A, and is included in the quiescent I_{CCAUX} numbers in the <u>Spartan-3AN FPGA data sheet</u>. Standby mode applies whenever the ISF memory is de-selected (CSB pin is High for 35 μ s or longer). Table 7-1 outlines the ISF dynamic current consumption requirements.

Table 7-1: Power-Related ISF Memory Guidelines (V_{CCAUX}=3.6V)

Description	Condition	Тур	Max	Units
Active current during read operation	$F_{CLK} = 20 \text{ MHz}$	7	10	mA
from In-System Flash memory array	$F_{CLK} = 33 \text{ MHz}$	8	12	mA
	$F_{CLK} = 50 \text{ MHz}$	11	15	mA
Active current during read operation from SRAM page buffer	$F_{CLK} = 20 \text{ MHz}$	_	20	mA
Active current during an In-System Flash program or erase operation	_	12	17	mA

Notes:

1. Approximate values added to I_{CCAUX} in addition to FPGA requirements.

Active Mode

The ISF memory is in the Active mode whenever the FPGA application drives the SPI_ACCESS CSB pin Low. The amount of power consumed depends on the operation and the CLK frequency, as shown in Table 7-1.

Standby Mode

The ISF memory initially powers up in Standby mode. The ISF memory also automatically re-enters Standby mode whenever the CSB input on the SPI_ACCESS primitive is High longer than 35 μ s. The associated current drops to approximately 100 μ A.



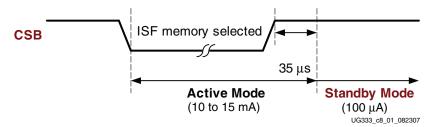


Figure 7-1: ISF Memory Enters Standby Mode when CSB is High Longer than 35 μs

Thermal Considerations

The ISF memory has negligible effect on the thermal considerations for the FPGA. The junction temperature of the ISF memory will be the same as the junction temperature calculated for the FPGA.



Sector-Based Program/Erase Protection

The Spartan®-3AN FPGA In-System Flash (ISF) memory supports various mechanisms to protect stored data against accidental or intentional changes.

- The **Sector Protection** feature provides the ability to selectively write-protect individual ISF memory sectors.
- The Sector Lockdown feature permanently locks a selected ISF memory sector, essentially converting the Flash memory into read-only ROM. Once a sector is locked down, it cannot be erased or modified.

Table 8-1 describes how these features affect a specific memory sector and how the features interact together.

Table 8-1: Sector Protect and Sector Lockdown Affect Memory Sector Program/Erase Functionality

Sector Prot	ect Feature	Sector Lockdown	Fun	ction	ality				
Global Control	Sector-Spec	cific Control		Σ					
Sector Protect Enable/Disable Status ⁽¹⁾	Sector Protect Status ⁽²⁾	Sector Lockdown Status ⁽³⁾	READ	PROGRAM	ERASE	Description			
N/A	OPEN	OPEN	•	•	•	All operations are possible. The FPGA			
DISABLE	PROTECTED	OPEN	•	•	•	application can read, program, and erase all locations in the sector.			
ENABLE	PROTECTED	OPEN	•			Temporarily Read-Only. The FPGA application can only read locations in the sector. In order to program or erase the sector, the application must either issue the Sector Protection Disable command or issue the Sector Protection Register Erase command followed by a Sector Protection Register Program command where the sector protection control byte is changed to OPEN.			
N/A	N/A	LOCKED	•			Permanently Read-Only. The sector can never again be programmed or erased.			

^{1.} Issue the Sector Protection Enable command to enable the protection settings defined in the Sector Protection Register. Issue the Sector Protection Disable command to unprotect all sectors.

^{2.} The sector protection setting is defined by the Sector Protection Register. To program a new value, the FPGA application must first issue the Sector Protection Register Erase command followed by a Sector Protection Register Program command.

^{3.} To lock a specific sector, issue the Sector Lockdown Program command.



Sector Protection

Using Sector Protection, the FPGA application protects selected memory sectors against erroneous program and erase cycles. There are five commands associated with the Sector Protection feature, as summarized in Table 8-2.

Table 8-2: Sector Protection Commands

Command	Function	Hexadecimal Command Sequence
Sector Protection Register Read	Read the contents of the Sector Protection Register to determine which ISF memory sectors are protected against accidental erase or program operations, assuming that protecting is enabled using the Sector Protection Enable command.	0x32
Sector Protection Register Erase	Erase the Sector Protection Register. Required before programming the Sector Protection Register.	0x3D + 0x2A + 0x7F + 0xCF
Sector Protection Register Program	Program the control bytes within the Sector Protection Register to protect selected sectors against program or erase operations. Erase the Sector Protection Register before programming.	0x3D + 0x2A + 0x7F + 0xFC
Sector Protection Enable	Enables protection for the sectors specified in the Sector Protection Register.	0x3D + 0x2A + 0x7F + 0xA9
Sector Protection Disable	Disables protection for all sectors.	0x3D + 0x2A + 0x7F + 0x9A

Sector Protection Status at Power-Up

At power-up, the Sector Protection feature is disabled, meaning that the FPGA application has full program and erase access to all sectors.

If the application employs the Sector Protection feature, then the FPGA application should issue the Sector Protection Enable command immediately after the FPGA is configured.

Sector Protection Register

The nonvolatile Sector Protection Register specifies which sectors are presently protected or unprotected. The Sector Protection Register contains between four to 16 bytes of data, depending on the specific Spartan-3AN FPGA as shown in Table 8-3. The Sector Protect control location directly corresponds to the associated ISF memory sector. For example, control byte 1 protects or unprotects to Sector 1, etc.

The specification for Sector 0 differs from the other sectors because Sector 0 is actually subdivided into two smaller sectors of different sizes. The byte-level description for the Sector 0 control appears in Table 8-4.

The FPGA application can modify the Sector Protection Register contents, although the register must first be erased using the Sector Protection Register Erase command.

Sector Protection is not active until the Sector Protection Register is programmed and the FPGA application issues the Sector Protection Enable command.

As shipped from Xilinx, all ISF memory sectors are unprotected (0x00).



Available Sectors Protection Status Sector/ XC3S200AN **XC3S700AN Control Byte** XC3S50AN **PROTECT** OPEN **XC3S400AN** XC3S1400AN 0 (special) (see Table 8-4) Sectors Bytes 0xFF 0x001 2 • **♦ ♦** ω 3 • • П Sectors Note 1 • 4 Bytes Note 1 • 5 Note 1 **♦ ♦** 6 16 ω 7 Note 1 П Sectors N/A N/A ***** 8 9 N/A N/A N/A N/A • 10 9 N/A N/A 11 N/A N/A 12 N/A N/A 13 N/A N/A 14 N/A N/A **♦** 15

Table 8-3: Sector Protection Register (one control byte per sector)

Notes:

1. The XC3S50AN TQ(G)144 ISF from UMC has 8 sectors. See "In-System Flash Change," page 14.

Table 8-4: Sector 0a and Sector 0b Protection Settings (Byte 0 in Table 8-3)

Sector Function	Sect	Sector 0a		Sector 0b		Don't Care			
Sector Function	7	6	5	4	3	2	1	0	Value
Sectors 0a and 0b unprotected	0	0	0	0	Χ	X	Х	Х	0x00
Protect Sector 0a	1	1	0	0	X	Х	X	X	0xC0
Protect Sector 0b	0	0	1	1	X	Х	X	X	0x30
Protect both Sector 0a and Sector 0b	1	1	1	1	Х	Х	Х	Х	0xF0

Sector Protection Register Erase

The Sector Protection Register must be erased before it can be programmed. Use the Sector Protection Register Erase command sequence to erase the register.

To issue the Sector Protection Register Erase command sequence, the FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Sector Protection Register
 Erase command sequence shown in Table 8-5 on the MOSI pin, most-significant bit of
 each byte first.



Table 8-5: Sector Protection Register Erase Command Sequence

Pin	Four-byte Command Sequence									
FIII	Byte 1	Byte 1 Byte 2 Byte 3 Byte 4								
MOSI	0x3D	0x2A	0x7F	0xCF						

After clocking in the last bit of the command sequence, deassert the CSB pin High.

A Low-to-High transition on the CSB input completes the command sequence and the ISF memory then erases the Sector Protection Register. The erase operation is internally self-timed and completes in the Page Erase time, T_{PE} , shown in Table 5-4, page 56 and specified in the <u>Spartan-3AN FPGA data sheet</u>. During this time, the <u>READY/BUSY</u> bit (bit 7) of the <u>Status Register</u> indicates whether the Sector Protection Register Erase operation is in progress or whether it has completed.

If the FPGA V_{CCAUX} power supply is interrupted before the erase cycle completes, then the content of the Sector Protection Register is not guaranteed.

The Sector Protection Register can be erased regardless if sector protection is enabled or disabled. The erased state of each byte in the Sector Protection Register is <code>0xff</code>, which protects each sector. Leave sector protection enabled while erasing of the Sector Protection Register, which then prevents accidental programming or erasing of the device. If the FPGA application should issue an erroneous program or erase command immediately after erasing the Sector Protection Register and before the register is reprogrammed, then the erroneous program or erase command is prevented.

Sector Protection Register Program

Once the Sector Protection Register is erased, reprogram the register using the Sector Protection Register Program command sequence.

To issue the Sector Protection Register Program command sequence, the FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Sector Protection Register Program command sequence shown in Table 8-6 on the MOSI pin, most-significant bit of each byte first.

Table 8-6: Sector Protection Register Program Command Sequence

					Sector P	Sector Protection Register Value (byte locations corresponds to sector)							
	Four	byte Comr	mand Sag	uonoo		XC	3S700AN, 2	XC3S1400A	AN (1	6 bytes)			
Pin	Four-	byte Comi	nano seq	uence	XC3S200AN, XC3S400AN (8 bytes)								
						XC3S50AN (4 bytes) ⁽¹⁾							
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6	Byte 7	Byte 8		Byte 12		Byte 20	
MOSI	0x3D	0x2A	0x7F	0xFC	Sector 0	Sector 1	Sector 2	Sector 3		Sector 7		Sector 15	

- 1. The XC3S50AN TQ(G)144 ISF from UMC has 8 bytes and 8 sectors. See "In-System Flash Change," page 14.
 - After clocking in the last bit of the command sequence, send the Sector Protection Register programming data on the MOSI pin.



- The number of bytes depends on the Spartan-3AN FPGA, as highlighted in Table 8-6 and Table 8-3, page 79.
 - The first data byte corresponds to Sector 0, the second data byte to Sector 1, and so on.
 - The XC3S50AN FPGA requires four bytes. The XC3S50AN TQ(G)144 ISF from UMC requires eight bytes, even though only four sectors are supported by the Xilinx tools. See "In-System Flash Change," page 14.
 - The XC3S200AN and the XC3S400AN FPGAs each require 8 bytes.
 - The XC3S700AN and the XC3S1400AN FPGAs require 16 bytes.
 - If the proper number of data bytes is not clocked in before the CSB pin is deasserted, then the protection status of the sectors corresponding to the unwritten bytes is not guaranteed. For example, if the FPGA application only writes two bytes, then the protection status for the subsequent sectors is not guaranteed.
 - If the FPGA application writes more than required number of bytes to the Sector Protection Register, then the data wraps back around to the beginning of the register. For example, if the application writes nine bytes to the XC3S200AN, then the ninth byte actually overwrites the value for Sector 0.
- Sector 0 is subdivided into two smaller sectors, called Sector 0a and Sector 0b. See Table 8-4, page 79 for information on how to protect or unprotect Sector 0 locations.
- All sectors, other than Sector 0, use the same command byte, as shown in Table 8-3, page 79.
 - Write 0x00 to unprotect a sector.
 - Write 0xFF to protect a sector.
 - If a value other than 0x00 or 0xFF is clocked into the Sector Protection Register, then the protection status of the corresponding sector is not guaranteed.
- After clocking in the last data bit to program the register, drive the CSB pin High on the falling edge of CLK to end the command.

Caution! The Sector Protection Register Program command uses the Buffer 1 SRAM page buffer. Any data stored in Buffer 1 prior to issuing the Sector Protection Register Program command is destroyed.

A Low-to-High transition on the CSB input completes the command sequence and the ISF memory then programs the Sector Protection Register. The erase operation is internally self-timed and completes in the Page Programming time, T_{PP}, or between 4 to 6 ms as shown in Table 4-5, page 46 and specified in the <u>Spartan-3AN FPGA data sheet</u>. During this time, the <u>READY/BUSY</u> bit (bit 7) of the <u>Status Register</u> indicates whether the Sector Protection Register Program operation is in progress or whether it has completed.

If the FPGA V_{CCAUX} power supply is interrupted before the programming operation completes, then the content of the Sector Protection Register is not guaranteed.

The FPGA application can always erase and program the Sector Protection Register regardless of the sector protection status.



Unprotecting Sectors While Sector Protection Enabled

Reprogramming the Sector Protection Register while sector protection is enabled allows the FPGA application to temporarily unprotect an individual sector or sectors rather than disabling the sector protection mechanism completely. However, there are limitations to this technique as described below.

Sector Protection Register Limited to 10,000 Program/Erase Cycles

The Sector Protection Register is limited to 10,000 erase/program cycles. If, as described above, the FPGA application modifies the Sector Protection Register to temporarily unprotect an individual sector or sectors, then the application must limit this practice to 10,000 cycles. Instead, use a combination of the techniques below.

- Temporarily unprotect individual sectors, but no more than 10,000 cycles
- Use the Sector Protection Enable and Sector Protection Disable commands to completely enable or disable the sector protection mechanism.

Sector Protection Register Read

To read the Sector Protection Register contents, issue the Sector Protection Register Read command sequence. The FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Sector Protection Register Read command sequence shown in Table 8-7 on the MOSI pin, most-significant bit of each byte first. The last 3 bytes are dummy bytes.

Table 8-7: Sector Protection Register Read Command Sequence

					Sector Protection Register Value (byte locations corresponds to sector)								
	Four-byte Command Sequence					XC3S700AN, XC3S1400AN (16 bytes)							
Pin						XC3S200AN, XC3S400AN (8 bytes)							
	Command	[Oon't Care	е		XC3S50AN	(4 bytes) ⁽¹⁾	oytes) ⁽¹⁾					
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6	Byte 7	Byte 8		Byte 12		Byte 20	
MOSI	0x32	XX	XX	XX	XX XX XX XX .					XX		XX	
MISO					Sector 0	Sector 0 Sector 1 Sector 2 Sector 3 Sector 7 Sector						Sector 15	

- 1. The XC3S50AN TQ(G)144 ISF from UMC has 8 bytes and 8 sectors. See "In-System Flash Change," page 14.
 - After clocking in the last bit of the command sequence, read the Sector Protection Register contents on the MISO pin.
 - ◆ The number of bytes depends on the Spartan-3AN FPGA, as highlighted in Table 8-7 and Table 8-3, page 79.
 - The first data byte corresponds to Sector 0, the second data byte to Sector 1, and so on.
 - The XC3S50AN FPGA provides four bytes. The XC3S50AN TQ(G)144 ISF from UMC requires eight bytes, even though only four sectors are supported by the Xilinx tools. See "In-System Flash Change," page 14.



- The XC3S200AN and the XC3S400AN FPGAs each provide 8 bytes.
- The XC3S700AN and XC3S1400AN FPGAs provide 16 bytes.
- If the FPGA application reads more than required number of bytes from the Sector Protection Register, any additional data provided on the MISO pin is undefined.
- After clocking the last data bit to read the register, deassert the CSB pin High.

Sector Protection Enable

The Sector Protection Enable command applies the protection level specified in the Sector Protection Register. To issue the Sector Protection Enable command sequence, the FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Sector Protection Enable command sequence shown in Table 8-8 on the MOSI pin, most-significant bit of each byte first.

Table 8-8: Sector Protection Enable Command Sequence

Pin		Four-byte Command Sequence								
	Byte 1	Byte 1 Byte 2 Byte 3 Byte 4								
MOSI	0x3D	0x2A	0x7F	0xA9						

• After clocking in the last bit of the command sequence, drive the CSB pin High on the falling edge of CLK. The defined sector protection level is now active.

Sector Protection Disable

The Sector Protection Disable command removes protection from all sectors. To issue the Sector Protection Disable command sequence, the FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Sector Protection Disable command sequence shown in Table 8-9 on the MOSI pin, most-significant bit of each byte first.

Table 8-9: Sector Protection Disable Command Sequence

Pin		Four-byte Command Sequence											
	Byte 1	Byte 2	Byte 3	Byte 4									
MOSI	0x3D	0x2A	0x7F	0x9A									

 After clocking in the last bit of the command sequence, drive the CSB pin High on the falling edge of CLK. Sector protection is now removed from all sectors.



Sector Lockdown

The ISF memory provides a mechanism called Sector Lockdown that permanently and irreversibly protects the contents of an individual sector against any program and erase cycles. Sector Lockdown effectively converts the erasable Flash memory sector to a one-time programmable (OTP), read-only memory (ROM).

Sector Lockdown is useful in applications to prevent malicious attempts to alter the FPGA configuration bitstream, program code, or security information. To prevent accidental changes or to have selective protection, see "Sector Protection," page 78.

Caution! Once an ISF memory sector is locked down, it can never be erased, programmed, or unlocked. Locking down a sector is irreversible.

There are two commands associated with the Sector Lockdown feature, as shown in Table 8-10.

Table 8-10: Sector Lockdown Commands

Command	Function	Hexadecimal Command Sequence
Sector Lockdown Register Read	Read the contents of the Sector Lockdown Register to determine the current ISF memory settings.	0x35
Sector Lockdown Program	Lock down a specific Sector.	0x3D + 0x2A + 0x7F + 0x30

Sector Lockdown Program

To lock down a specific sector, issue a Sector Lockdown Program command, followed by a 24-bit sector address, anywhere within the memory sector to be locked down.

To issue the Sector Lockdown Program command, the FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Sector Lockdown Program command sequence shown in Table 8-11 on the MOSI pin, most-significant bit of each byte first.

Table 8-11: Sector Lockdown Program Command Sequence

Pin	Fou	ır-byte Comı	mand Seque	24-bit Address						
PIII	Four-byte Command Sequence Byte 1 Byte 2 Byte 3 0x3D 0x2A 0x7F	Byte 4	Byte 5	Byte 6	Byte 7					
MOSI	0x3D	0x2A	0x7F	0x30	Default Ad See Table 5 page 61. Power-of-2 Addressing Table A-6,	XX				

- Immediately following the four-byte command code, serially clock in a 24-bit Sector address.
 - Sector 0 is different than all other sectors.
 - Sector 0 is subdivided into two subsectors called Sector 0a and Sector 0b.



- Sector 0a and Sector 0b are each erased individually and require a unique address with additional addressing bits, different than all the other sectors.
- The page address and byte address bits, which follow the Sector Address, specify any valid address location within the sector which is to be erased.
- If using the default address scheme, see Table 5-10, page 61.
- If using power-of-2 addressing, see Table A-6, page 97.
- After clocking in the last bit of the 24-bit address, drive the CSB pin High on the falling edge of CLK.

A Low-to-High transition on the CSB input completes the command sequence and the ISF memory then programs the Sector Lockdown Register. The erase operation is internally self-timed and completes in the Page Programming time, T_{PP}, or between 4 to 6 ms as shown in Table 4-5, page 46 and specified in the <u>Spartan-3AN FPGA data sheet</u>. During this time, the READY/BUSY bit (bit 7) of the Status Register indicates whether the Sector Lockdown Program operation is in progress or whether it has completed.

If the FPGA V_{CCAUX} power supply is interrupted before the programming operation completes, then the content of the Sector Lockdown Register is not guaranteed. If power is interrupted, read the Sector Lockdown Register to determine if it was programmed correctly. If no, reissue the Sector Lockdown Program command, if necessary.

Sector Lockdown Register

The nonvolatile Sector Lockdown Register indicates which sectors are open and which are permanently locked down. The Sector Lockdown Register contains between four to 16 bytes of data, depending on the specific Spartan-3AN FPGA as shown in Table 8-12. The Sector Lockdown status byte location directly corresponds to the associated ISF memory sector. For example, status byte 1 corresponds to the lockdown status of Sector 1, etc.

The specification for Sector 0 differs from the other sectors because Sector 0 is actually subdivided into two smaller sectors of different sizes. The byte-level description for the Sector 0 status appears in Table 8-13.

The Lockdown Status for a specific sector is updated based on a Sector Lockdown Program command. The Sector Lockdown Register is a read-only location and cannot be directly modified.



Available Sectors Lockdown Status Sector/ XC3S200AN **XC3S700AN Status Byte** XC3S50AN **LOCKED** OPEN **XC3S400AN** XC3S1400AN (see Table 8-13) • 0 (special) Sectors Bytes **\ ♦** 1 0xFF 0x002 • **♦ ♦** ω 4 3 **** • • Ш Sectors Note 1 • • 4 Bytes Note 1 • 5 Note 1 **♦ ♦** 6 = 16 ω 7 Note 1 **♦** Sectors N/A N/A ***** 8 N/A 9 N/A N/A N/A • 10 9 N/A N/A **♦** 11 N/A N/A 12 N/A N/A 13 • N/A N/A 14

Table 8-12: Sector Lockdown Register (Read-Only)

Notes:

N/A

N/A

15

Table 8-13:	Sector 0a a	and Sector 0b	Lockdown Settings	s (B	yte 0 in	Table 8-12)
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♦

Sector Function	Sect	or 0a	Sect	or 0b		Hex			
Sector Function	7	6	5	4	3	2	1	0	Value
Sectors 0a and 0b unlocked	0	0	0	0	0	0	0	0	0x00
Sector 0a locked down	1	1	0	0	0	0	0	0	0xC0
Sector 0b locked down	0	0	1	1	0	0	0	0	0x30
Both Sector 0a and Sector 0b locked down	1	1	1	1	0	0	0	0	0xF0

Sector Lockdown Register Read

The FPGA application can read the Sector Lockdown Register to determine which sectors in the memory array, if any, are permanently locked down.

To read the Sector Lockdown Register contents, issue the Sector Lockdown Register Read command sequence. The FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Sector Lockdown Register Read command sequence shown in Table 8-14 on the MOSI pin, most-significant bit of each byte first. The last 3 bytes are dummy bytes.

The XC3S50AN TQ(G)144 ISF from UMC has 8 bytes and 8 sectors. See "In-System Flash Change," page 14.



Table 8-14: Sector Lockdown Register Read Command Sequence

					Sector Lockdown Register Value (byte location corresponds to sector)												
	Four-by	te Comm	and Sequ	ience		XC	3S700AN, 2	XC3S1400A	AN (1	6 bytes)							
Pin						XC3S200AN, XC3S400AN (8 bytes)											
	Command	[Oon't Care	е		XC3S50AN (4 bytes) ⁽¹⁾											
	Byte 1	Byte 2	Byte 2 Byte 3 Byte 4		Byte 5	Byte 6	Byte 7	7 Byte 8		Byte 12		Byte 20					
MOSI	0x35	XX	XX	XX	XX	XX	XX XX			XX		XX					
MISO					Sector 0	Sector 1	Sector 2	Sector 3	•••	Sector 7		Sector 15					

- 1. The XC3S50AN TQ(G)144 ISF from UMC has 8 bytes and 8 sectors. See "In-System Flash Change," page 14.
 - After clocking in the last bit of the command sequence, read the Sector Lockdown Register contents on the MISO pin.
 - ◆ The number of bytes depends on the Spartan-3AN FPGA, as highlighted in Table 8-14 and Table 8-3, page 79.
 - The first data byte corresponds to Sector 0, the second data byte to Sector 1, and so on.
 - The XC3S50AN FPGA provides four bytes. The XC3S50AN TQ(G)144 ISF from UMC provides eight bytes, even though only four sectors are supported by the Xilinx tools. See "In-System Flash Change," page 14.
 - The XC3S200AN and the XC3S400AN FPGAs each provide 8 bytes.
 - The XC3S700AN and the XC3S1400AN FPGAs provide 16 bytes.
 - If the FPGA application reads more than required number of bytes from the Sector Lockdown Register, any additional data provided on the MISO pin is undefined.
 - After clocking the last data bit to read the register, drive the CSB pin High.





Security Register

The Spartan®-3AN FPGA In-System Flash (ISF) memory includes a special 128-byte Security Register, shown in Table 9-1.

Security Register

The 128 bytes are further divided into two subfields.

• The **User-Defined Field** (byte locations 0 through 63), can be programmed with any value at any time, but it can only be programmed once. In other words, this field is one-time programmable (OTP). The default delivered state is erased, and all locations are 0xFF.

Caution! Once the 64-byte User-Defined Field is programmed, it cannot be erased or changed.

• The **Unique Identifier** (byte locations 64 through 127) is programmed during Xilinx factory manufacturing and contains a unique identifier per each ISF memory. This field is different from the Device DNA feature accessible within Spartan-3A and Spartan-3AN FPGAs. The factory-programmed data cannot be erased or changed.

Table 9-1: Security Register Contents

	Security Register (128 bytes)													
Byte	User	-Defined Fie	eld (64 b	ytes)	Factory ID (64 bytes)									
	0	1		63	64	65		127						
Description						Unique identifier for each ISF memory inside each Spartan-3AN FPGA								
Number of Programming Cycles	(this field is	1 s one-time pr	rogramn	nable, OTP)										

The Security Register serves a variety of potential applications, such as uniquely identifying a particular ISF memory device, for protecting FPGA bitstreams or user data, or for locked key storage. Applications and usage are similar to that for the FPGA Device DNA register. See the *Protecting FPGA Designs* chapter in <u>UG332</u>, <u>Spartan-3 Generation Configuration User Guide</u>.

Security Register Program

Only the User-Defined Field in the Security Register is programmable. This field does not need to be erased before it is programmed.



To issue the Security Register Program command sequence, the FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Security Register Program command sequence shown in Table 9-2 on the MOSI pin, most-significant bit of each byte first.

Table 9-2: Security Register Program Command Sequence

Pin	Four-	byte Comi	mand Seq	uence	Security Register Value (64-byte User-Defined Field)							
	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6		Byte68				
MOSI	0x9B	0x00	0x00	0x00	User-Field Data 0	User-Field Data 1		User-Field Data 63				

Notes:

- 1. The Security Register Program command is supported in simulation. The simulation model has a default Factory ID of 00. For simulation purposes, a user parameter can set the Factory ID to a different value (see Table 1-3).
- After clocking in the last bit of the command sequence, send the Security Register programming data on the MOSI pin
 - Specify all 64 bytes.
 - The content of any unwritten locations is not guaranteed.
 - If more than 64 bytes are provided, then the additional data wraps around starting again at location 0.
 - Specify each byte location serially, most-significant bit first.
- After clocking in the last data bit to program the register, drive the CSB pin High on the falling edge of CLK.

A Low-to-High transition on the CSB input completes the command sequence. The programming operation is internally self-timed and completes in the Page Programming time, T_{PP}, shown in Table 4-5, page 46 and specified in the <u>Spartan-3AN FPGA data sheet</u>. During this time, the <u>READY/BUSY</u> bit (bit 7) of the <u>Security Register</u> indicates whether the Security Register Program operation is in progress or whether it has completed.

Caution! If the FPGA V_{CCAUX} power supply is interrupted before the erase cycle completes, then the content of the 64-byte User-Defined Field within the Security Register is not guaranteed.

Caution! If less than 64 bytes of data is clocked in before the CSB pin is deasserted, then the values for any unspecified byte locations are not guaranteed. For example, if only the first two bytes are clocked in rather than the complete 64 bytes, then the remaining 62 bytes of the User-Defined Field within the Security Register are not guaranteed.

Caution! The User-Defined Field within the Security Register can only be programmed once. Consequently, it is not possible to program only the first two bytes of the register and then later program the remaining 62 bytes.

Caution! The Security Register Program command uses the SRAM page Buffer 1 for temporary data storage. Consequently, this command overwrites any previous contents of Buffer 1.



Security Register Read

To read the Security Register, the FPGA application must perform the following actions using the SPI_ACCESS design primitive.

- Drive CSB Low while CLK is High or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the four-byte Security Register Read command sequence shown in Table 9-3 on the MOSI pin, most-significant bit of each byte first. The last 3 bytes are dummy bytes.

Table 9-3: Security Register Read Command Sequence

	Four-b	rto Comm	nand Segi	ionco	Security Register											
Pin	rour-by	yte Collin	delice	Us	er-Define	eld	Unique Identifier									
	Byte 1 Byte 2 Byte 3 B			Byte 4	Byte 5 Byte 6			Byte 68	Byte 69	Byte 70		Byte 132				
MOSI	0x77	XX	XX	XX	XX	XX		XX	XX	XX		XX				
MISO		Hig	Data 0	Data 1		Data 63	Data 64	Data 65		Data 127						

- 1. The Security Register Read command is supported in simulation.
 - After clocking in the last bit of the command sequence, receive the Security Register data on the MISO pin
 - Receive each byte location serially, most-significant bit first.
 - The FPGA application can read less than the complete 128 bytes. For example, the application can stop after reading first few bytes of the User-Defined Field.
 - Any data beyond the end of the 128-byte Security Register is undefined.
 - After clocking in the last data bit to program the register, drive the CSB pin High on the falling edge of CLK.





Optional Power-of-2 Addressing Mode

As initially shipped, the Spartan®-3AN FPGA In-System Flash (ISF) memory uses the Default Addressing Mode, highlighted in Table 2-2, page 22. The Default Addressing Mode provides 3% more total bits, providing additional "extra" bits and bytes within each page for potential file system control and error correction applications.

For some applications, however, a power-of-2 binary addressing method may prove more natural. The ISF memory supports such an addressing mode, as highlighted in Table A-3, page 95, but does require an additional irreversible programming step, described below. Typically, this step is performed on a production tester and not by the FPGA application itself.

Caution! The Power-of-2 Addressing Mode is not supported in simulation. Simulation only supports the Default Addressing Mode.

Caution! Changing over to the power-of-2 addressing mode is irreversible. Once the FPGA's In-System Flash memory (ISF) is programmed for this mode, it cannot be changed back to the Default Addressing Mode.

Caution! Immediately after Permanently Changing to the Power-of-2 Addressing Mode, the FPGA's power supply must be cycled off and on before the change takes effect.

Caution! Any data stored while the FPGA ISF memory was in the Default Addressing Mode, such as FPGA configuration bitstreams, is corrupted once the ISF memory is irreversibly changed over to the Power-of-2 addressing mode. The ISF memory must be erased and rewritten after changing to the optional power-of-2 addressing mode.

Table A-1 illustrates how the addressing mode affects total memory size.

Table A-1: Default Addressing Mode vs. Power-of-2 Addressing Mode

FPGA	Total Bits by Ad	ddressing Mode	Page Size by Addressing Mo						
FFGA	Default	Power-of-2	Default	Power-of-2					
XC3S50AN ⁽¹⁾ (X-FAB)	1,081,344	1,048,576							
XC3S50AN ⁽¹⁾ (UMC)	2,162,688	2,097,152	264 bytes	256 bytes					
XC3S200AN	4,325,376	4,194,304							
XC3S400AN	4,323,370	4,194,304							
XC3S700AN	8,650,752	8,388,608							
XC3S1400AN	17,301,504	16,777,216	528 bytes	512 bytes					

Notes:

1. The XC3S50AN with the UMC ISF has 2 Mbits of memory but only 1 Mbit is supported by the Xilinx tools. See "In-System Flash Change," page 14.



How to Determine the Current Addressing Mode

The Page Size bit, bit 0, in the Status Register indicates the current addressing mode, as outlined in Table 6-7, page 69. If required, the ISF memory programmer or the FPGA application can read the Status Register by issuing a Status Register Read command.

Permanently Changing to the Power-of-2 Addressing Mode

To permanently change over from the Default Addressing Mode to the optional power-of-2 addressing mode, the programmer or FPGA application must perform the following steps.

- Drive CSB Low while CLK is High, or on the rising edge of CLK.
- On the falling edge of CLK, serially clock in the Power-of-2 Page Size command sequence, shown in Table A-2, most-significant bit first.

Table A-2: Power-of-2 Page Size Command Sequence

	Four-byte Command Sequence											
Pin	Byte 1	Byte 2	Byte 3	Byte 4								
MOSI	0x3D	0x2A	0x80	0xA6								

- After clocking in the last bit of the command sequence, set CSB High to start the internally self-timed programming cycle.
- Wait at least the Page Programming time, T_{PP}, shown in Table 4-5, page 46 and specified in the <u>Spartan-3AN FPGA data sheet</u>. During this time, the <u>READY/BUSY</u> bit (bit 7) is '0' in the <u>Status Register</u>, indicating that an ISF memory programming operation is in progress.
- After the programming operation completes, the FPGA power supplies must be cycled off, then reapplied before the Power-of-2 addressing mode becomes active.
- Any data stored in the ISF memory prior to setting the Power-of-2 addressing mode will be corrupted. Erase and reprogram the ISF memory with the intended data.

If the FPGA is powered-down before the completion of the program cycle, then the Power-of-2 address setting cannot be guaranteed. Should this occur, however, check that the Page Size bit (bit 0) is set to '1' in the Status Register, indicating that the page size was successfully programmed. If not, re-issue the Power-of-2 Page Size command.



Power-of-2 Addressing Mode

All Spartan-3AN FPGAs are shipped supporting the Default Addressing Mode. The optional Power-of-2 Addressing mode is only available after Permanently Changing to the Power-of-2 Addressing Mode.

Power-of-2 Addressing

Table A-3 summarizes the address mapping for the optional power-of-2 addressing mode.

Table A-3: Power-of-2 Addressing Mode

		ı	Hig	h A	ddr	ess	3			M	idd	lle /	Add	Ires	s		Low Address							
FPGA	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Binary Address	0	0	0	A20	A19	A18	A17	A16	A15	A14	A13	A12	A11	A10	49	A8	A7	A6	A5	A4	A3	A2	A1	A0
3S50AN ⁽¹⁾ (X-FAB	0	0	0	0	0	0	0	Sec (4	tor 1)	Se	ctor	0a,	0b	X	X	Χ	Χ	X	X	X	X	X	Χ	X
ISF)								B	locl	k (6	4 bl	ock	s)	X	X	X	X	X	X	X	X	X	X	X
								F	age	e Ao	ldr	ess	(512	2 pa	iges	(3)	Ву	te 1	Ada	lres	s (2	256 1	byte	es)
3S50AN ⁽¹⁾	0	0	0	0	0	0	Se	ctor	(8)	Se	ctor	0a,	0b	Χ	Χ	X	X	X	X	Χ	Χ	Χ	X	Χ
(UMC ISF)							Bl	ock	(12	28 b	locl	ks)		Χ	Χ	Χ	Χ	X	X	Χ	Χ	Χ	X	Χ
								Pag	e A	dd	ress	(1,	024	pag	ges)		Byte Address (256 bytes)					es)		
3S200AN	0	0	0	0	0	Se	ctor	(8)	S	ecto	or 0	a, 0	b	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ
3S400AN							Bl	ock	(25	56 b	locl	ks)		Χ	Χ	X	Χ	X	X	Χ	Χ	Χ	Χ	X
							Pa	age	Ad	dre	ss (2,04	18 p	age	s)		Ву	te .	Ada	lres	s (2	256 1	byte	es)
3S700AN	0	0	0	0	S	ecto	or (1	l6)	S	ecto	or 0	a, 0	b	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ
]	Blo	c k (512	blo	cks)		Χ	Χ	X	Χ	X	X	Χ	Χ	Χ	Χ	X
							Pag	ge A	dd	ress	(4,	096	pag	ges)			Ву	te .	Ada	lres	s (2	256 1	byte	es)
3S1400AN	0	0	0	S	ecto	or (1	l6)	S	ect	or 0	a, 0	b	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ
					l	Blo	ck (512	blo	cks)		Χ	Χ	Χ	X	Χ	X	X	Χ	Χ	Χ	X	Χ
						Pag	ge A	dd	ress	s (4,	096	pag	ges)]	Byte	e A	ddr	ess	(51	2 by	tes)
Binary Address	0	0	0	A20	A19	A18	A17	A16	A15	A14	A13	A12	A11	A10	A9	A8	A7	A6	A5	A4	A3	A2	A1	A0

Notes:

1. The XC3S50AN with the UMC ISF has 2 Mbits of memory but only 1 Mbit is supported by the Xilinx tools. See "In-System Flash Change," page 14.



Power-of-2 Page Addressing

Table A-4 summarizes how page addresses are specified within the 24-bit address field.

Table A-4: Page Address, Power-of-2 Addressing Mode

			Hig	h A	ddı	ess	6			M	lidd	lle /	٩dc	ires	s	Low Address									
FPGA	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0	
Binary Address	0	0	0	A20	A19	A18	A17	A16	A15	A14	A13	A12	A11	A10	49	A8	A7	A6	A5	A4	A3	A2	A1	A0	
3S50AN ⁽¹⁾ (X-FAB ISF)	0	0	0	0	0	0	0	I	Page	e Ao	ddr	ess	(51:	2 pa	iges	X	X	X	X	X	X	X	X		
3S50AN ⁽¹⁾ (UMC ISF)	0	0	0	0	0	0		Pag	ge A	ddi	ress	i (1,	024	paş	ı	X	X	X	X	X	X	X	X		
3S200AN	0	0	0	0	0		Pa	age	Ad	dre	ss (2,04	18 p	age	s)	,	Χ	Χ	Χ	Χ	Χ	X	X	Χ	
3S400AN	0	0	0	0	0		Pa	age	Ad	dre	ss (2,04	18 p	age	es)	•	Χ	X	Χ	Χ	Χ	Χ	Χ	Χ	
3S700AN	0	0	0	0			Page Address (4,096 pages)											Χ	Χ	Χ	Χ	Χ	Χ	Χ	
3S1400AN	0	0	0		Page Address (4,096 pages)											X	X	X	X	X	X	X	X		

Notes:

Power-of-2 Block Addressing

Table A-5 summarizes how block addresses are mapped into the 24-bit address field.

Table A-5: Block Addressing, Power-of-2 Addressing Mode

High Address										Middle Address									Low Address								
FPGA		22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0			
Binary Address	0	0	0	A20	A19	A18	A17	A16	A15	A14	A13	A12	A11	A10	49	A8	A7	9W	A5	A4	A3	A2	A1	Α0			
3S50AN (X-FAB ISF) ⁽¹⁾	0	0	0	0	0	0	0	I	Block (64 blocks)						Χ	Χ	Χ	Χ	X	Χ	Χ	Χ	Χ	Х			
3S50AN (UMC ISF) ⁽¹⁾	0	0	0	0	0	0	Block (128 blocks)							Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Х			
XC3S200AN	0	0	0	0	0		В	locl	(25	66 b	lock	s)		Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	X			
XC3S400AN	0	0	0	0	0 Block (256 blocks)									Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	X			
XC3S700AN	0	0	0	0	0 Block (512 blocks)									Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	X			
XC3S1400AN	0	0	0			Blo	ck (512	blo	cks)			Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Χ	X			

Notes:

1. The XC3S50AN with the UMC ISF has 2 Mbits of memory but only 1 Mbit is supported by the Xilinx tools. See "In-System Flash Change," page 14.

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Power-of-2 Sector Addressing

Table A-6 shows the sector addressing for the Power-of-2 addressing mode. Sector 0 is subdivided into two subsectors, designated as Sector 0a and Sector 0b. These subsectors require additional address bits.

Table A-6: Sector Addressing, Power-of-2 Addressing Mode

			Hig	jh A	ddr	ess				ľ	Mido	dle A	Add	res	S		Low Address									
FPGA /	FPGA / Sector		22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0	
Binary Address		0	0	0	A20	A19	A18	A17	A16	A15	A14	A13	A12	A11	A10	A9	A8	A7	A6	A5	A4	A3	A2	A1	A0	
XC3S50AN ⁽¹⁾	Sector	0	0	0	0	0	0	0	Sec	tor		J		J	J	D	on't	't Care bits								
(X-FAB ISF)	Sector 0a								0	0	0	0	0	0	X	XX	X	Χ	Χ	X	Χ	X	X	X	X	
	Sector 0b													1												
	Sectors 1–3								SA1	SA0	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	
XC3S50AN ⁽¹⁾	Sector	0	0	0	0	0	0	Sector			Don't Care bits															
(UMC ISF)	Sector 0a							0	0	0	0	0	0	0	X	X	X	X	X	X	X	X	X	X	X	
	Sector 0b													1												
	Sectors 1–7							SA2	SA1	SA0	Х	Х	Х	Х	Х	Х	X	Х	Х	X	Х	Х	Х	Х	х	
XC3S200AN	Sector	0	0	0	0	0	S	Sector								Don't Care bits										
XC3S400AN	Sector 0a						0	0	0	0	0	0	0	0	X	X	X	Χ	X	X	Χ	X	X	X	X	
	Sector 0b													1												
	Sectors 1–7						SA2	SA1	SA0	X	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	х	
XC3S700AN	Sector	0	0	0	0		Sec	ctor								Dor	ı't C	are	bits	3			*			
	Sector 0a					0	0	0	0	0	0	0	0	0	X	X	X	Χ	X	X	Χ	X	X	X	X	
	Sector 0b													1	-											
	Sectors 1–15					SA3	SA2	SA1	SA0	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	х	
XC3S1400AN	Sector	0	0	0		Sec	ctor								D	on't	Caı	re bi	its							
	Sector 0a				0	0	0	0	0	0	0	0	0	X	X	X	X	Χ	X	X	X	X	X	X	X	
	Sector 0b												1													
	Sectors 1–15				SA3	SA2	SA1	SA0	Х	Х	X	Х	Х	х	х	Х	X	Х	X	X	X	Х	X	Х	Х	

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